

Fundamental phenomena and applications of exciton-polariton condensates (I)

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Index

➔ Introduction

- Semiconductor laser.....VCSEL
- VCSELs & microcavities

➔ Polaritons

➔ Some key studies

- Polaritons in cavities, Rabi
- OPO
- BEC
- Vortices
- Superfluidity
- Patterning of cavities

Quantum cavities

⇒ Materials

- Atoms, structured materials, **semiconductors**


⇒ Requisites

- Cavity size comparable to characteristic λ
- Excellent control of sizes and compositions (n)

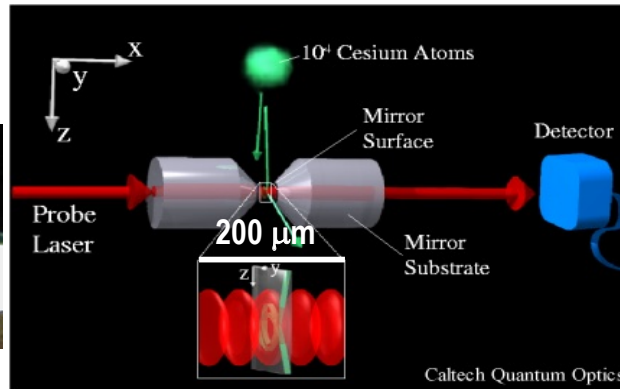
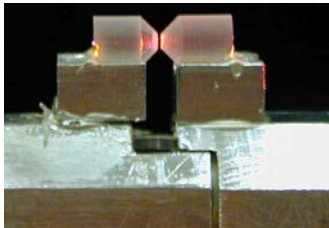
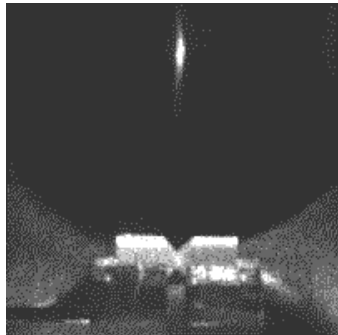
⇒ Physics

- Interactions: electronics excitations – electromagnetic modes
- Condensation

⇒ Applications

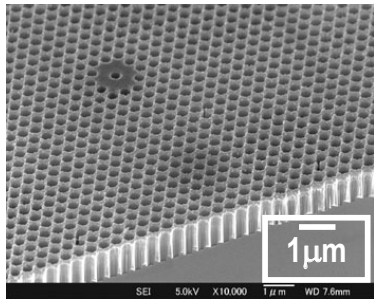
- Spontaneous emission control  decrease laser threshold
- Thersholdless lasers
- All optical devices
- Quantum information

Materials



Atoms

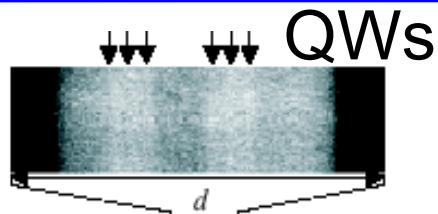
Real-Time Cavity QED with single atoms
Kimble et al. (Caltech)
Phys. Rev. Lett. **80** (1998)



Structured materials

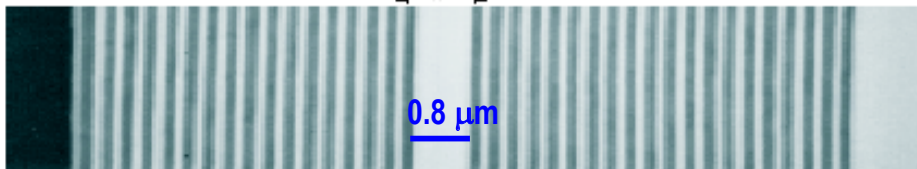
Photonic crystal with defects

Semiconductor And Materials Company (SAMCO). Kyoto. Japan



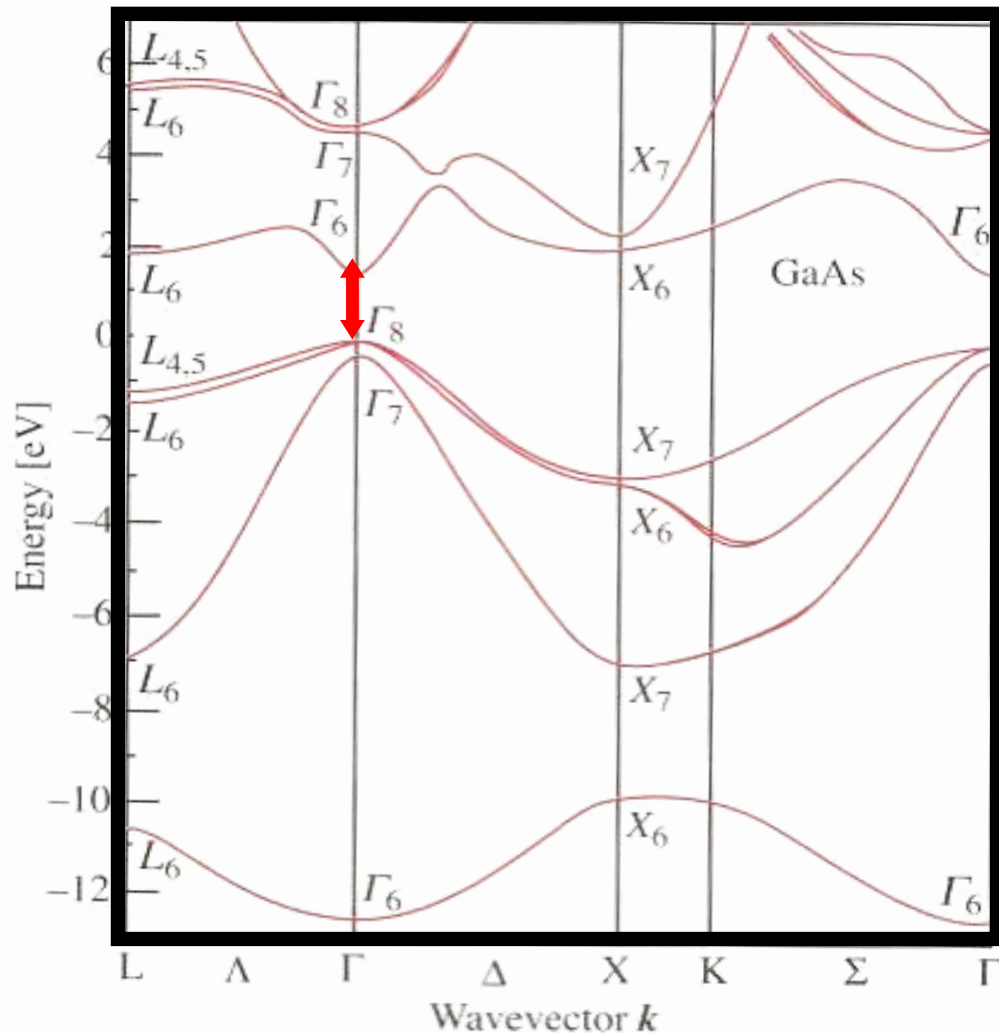
Semiconductors & QWs

R. André. Joseph Fourier Université. Grenoble, Francia



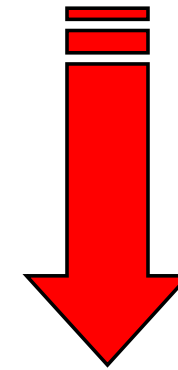
Semiconductor Laser (I)

Band structure



GaAs

Direct band gap

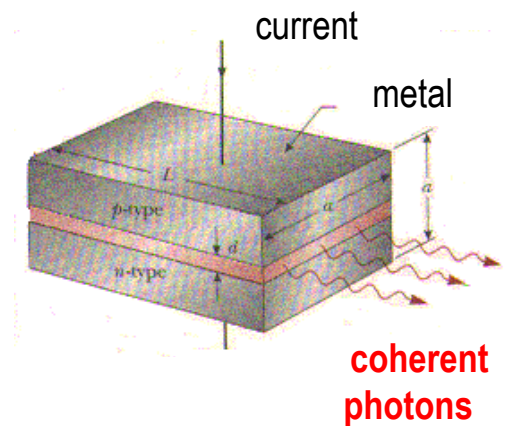
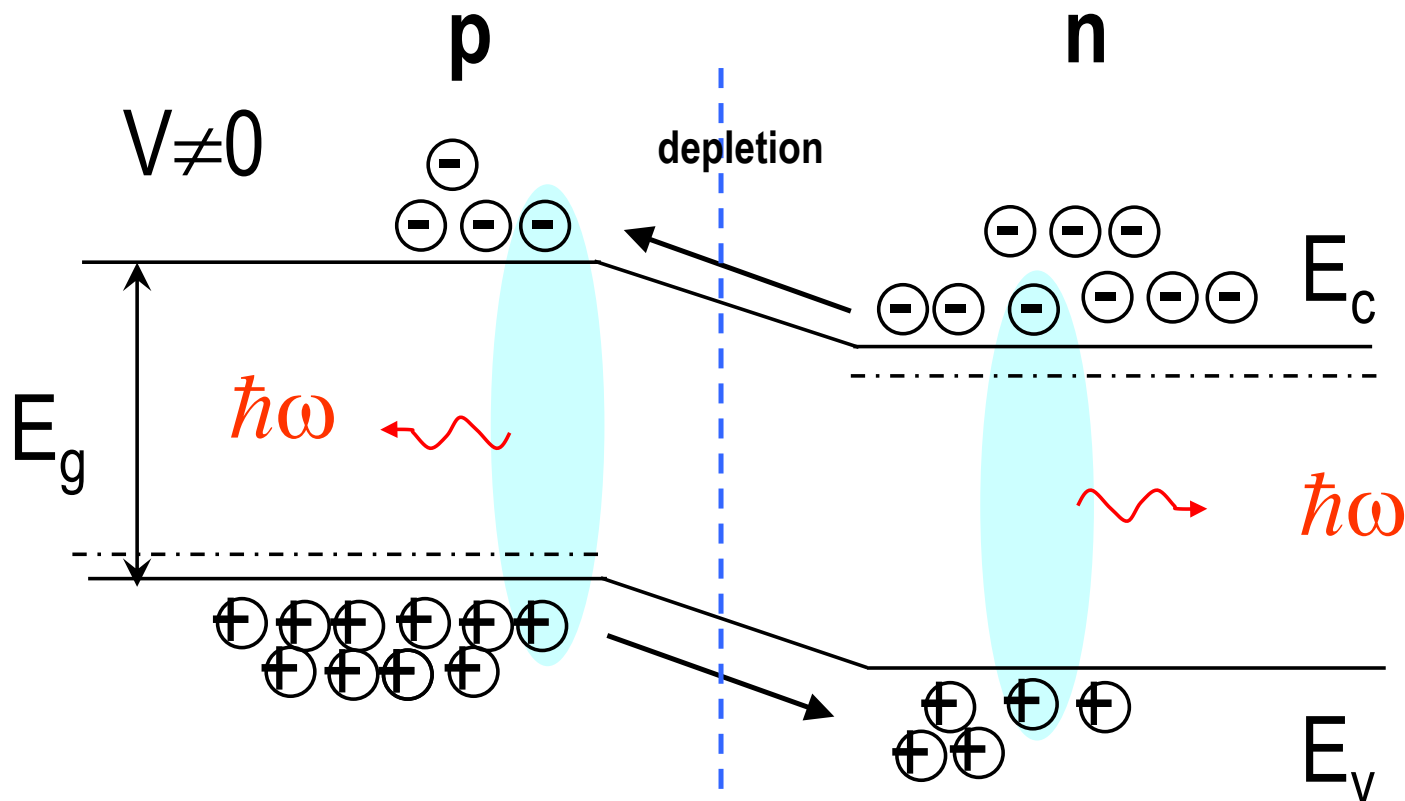


Light emission and absorption

Semiconductor Laser (II)

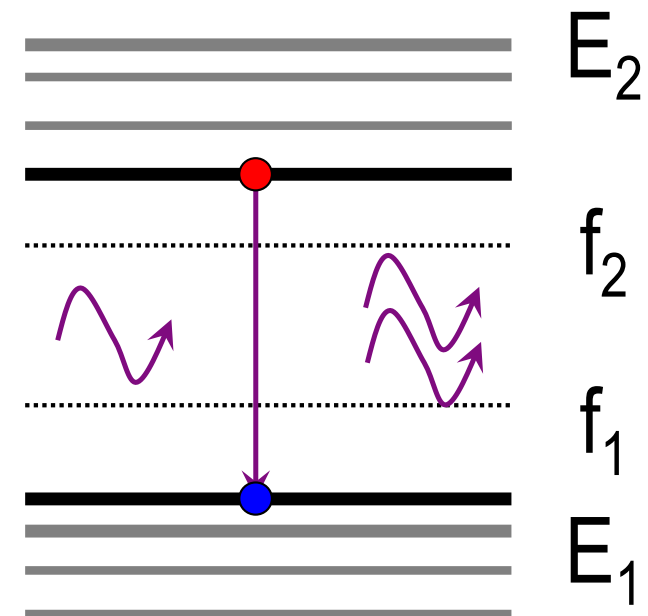
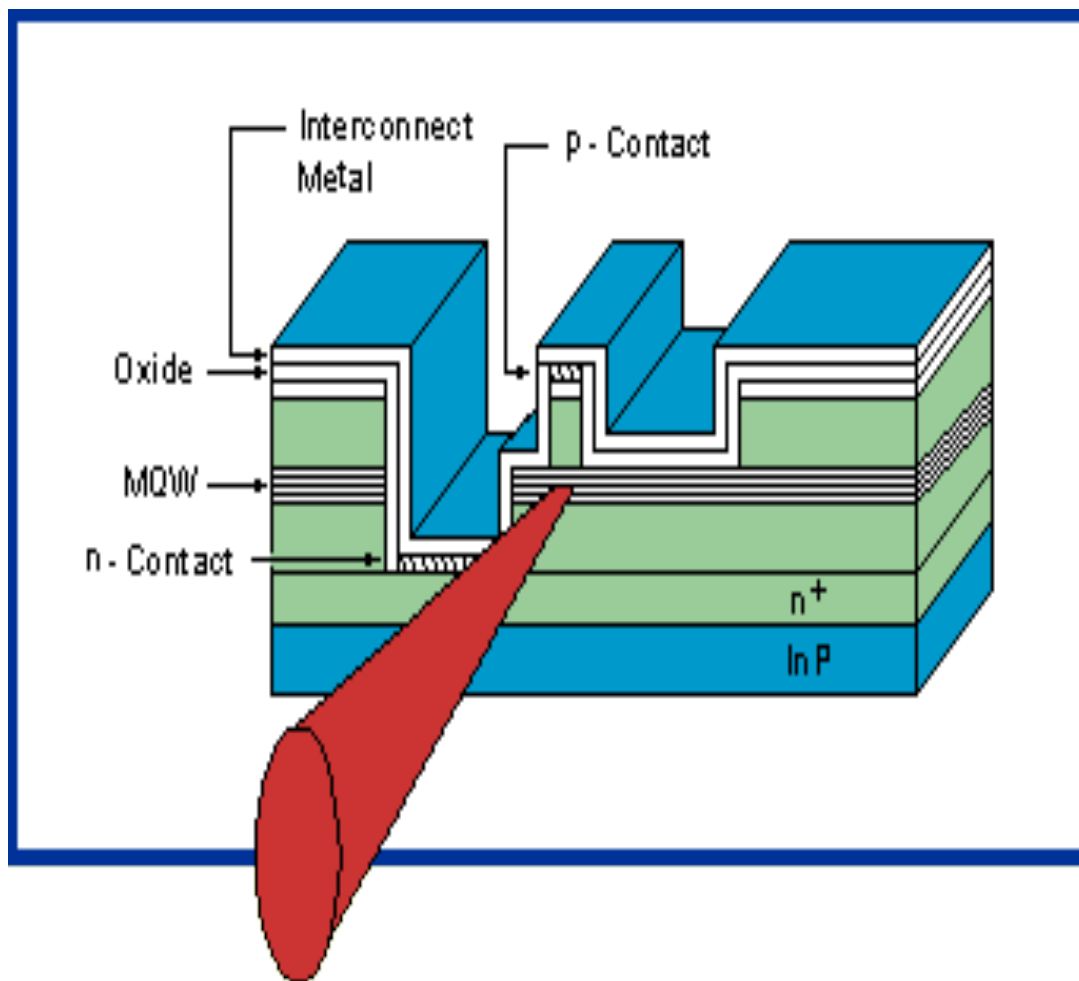
- ➔ Doping & carrier injection
- ➔ Homo-union

Light emission



Semiconductor Laser (III)

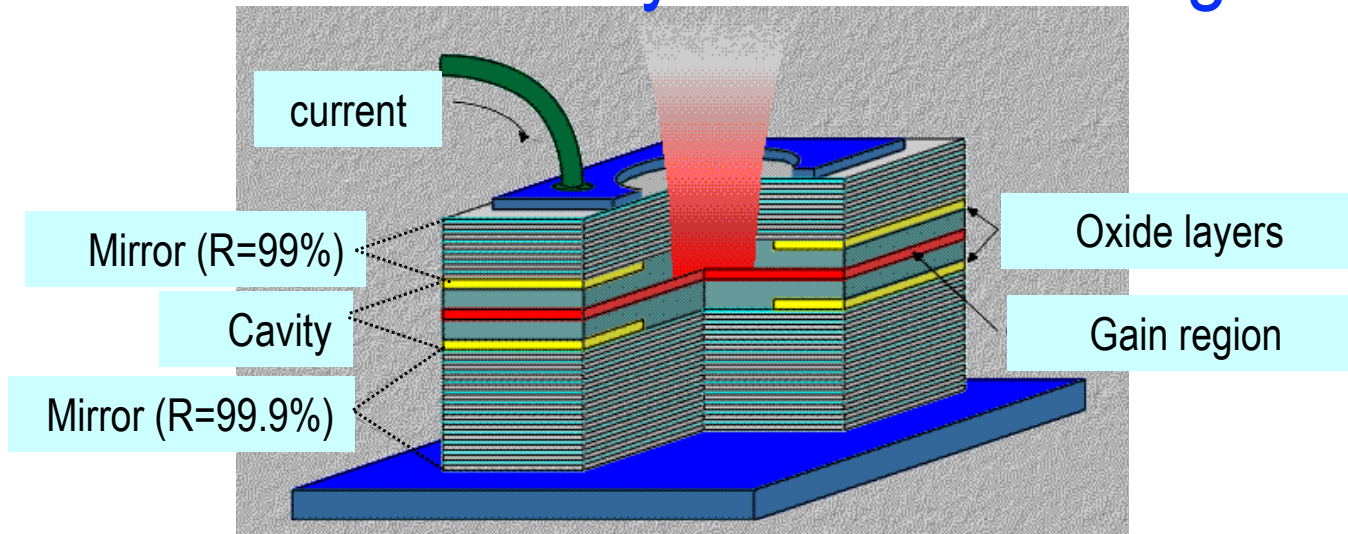
Confinement (quantum wells)



**Population inversion
&
stimulated emission**

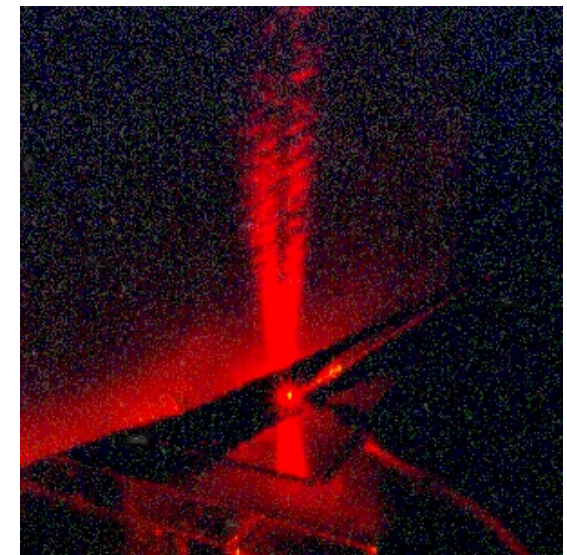
Semiconductor Laser (IV)

Vertical cavity surface emitting laser (VCSEL)



Advantages

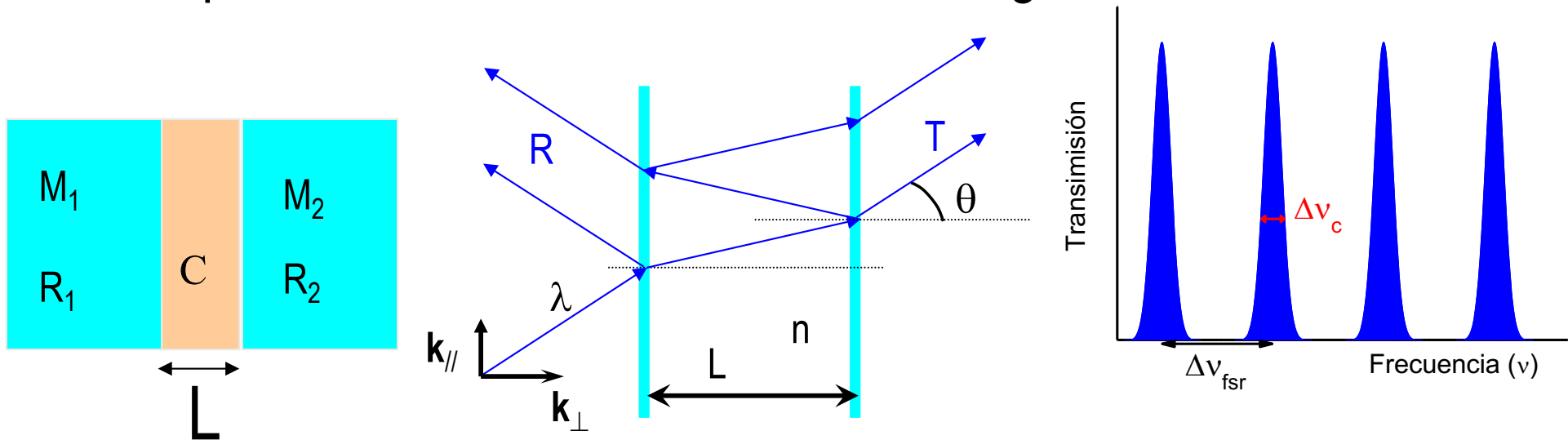
- ➔ Vertical emission
- ➔ Only a longitudinal mode
- ➔ Large efficiency/ low consumption
- ➔ Easiness of processing / testing



Laser cavity (I)

Fabry-Perot Resonator

➔ Simplest structure to confine electromagnetic fields



$$T = \frac{(1 - R_1)(1 - R_2)}{[(1 - \sqrt{R_1 R_2})^2 + 4\sqrt{R_1 R_2} \sin^2 \phi]}$$

$$\Delta \nu_{fsr} = \frac{c}{2\pi L \cos \theta}$$

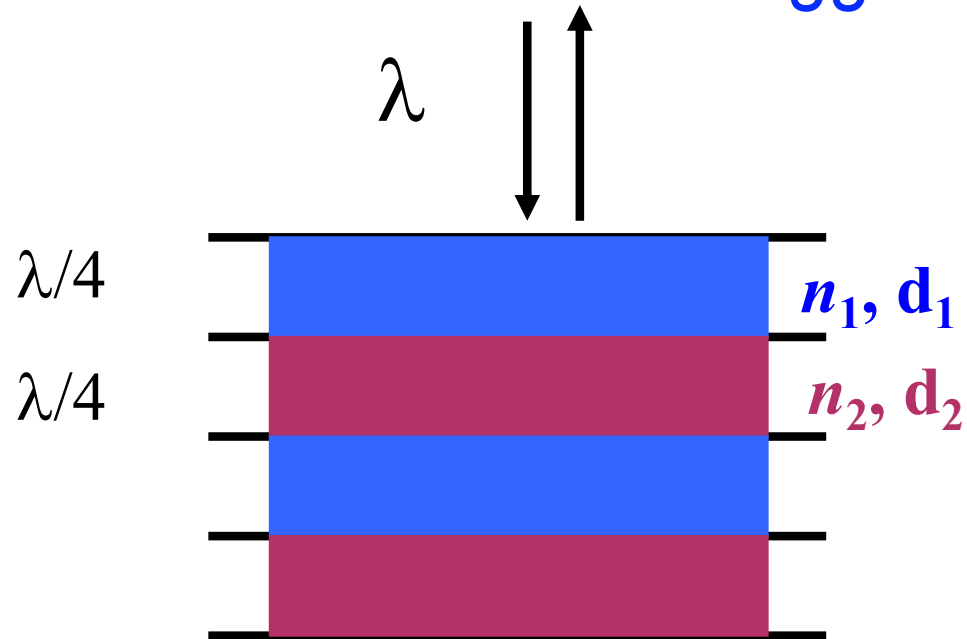
$$\Delta \nu_c = \frac{c}{2nL \cos \theta} \frac{1 - \sqrt{R_1 R_2}}{\pi (R_1 R_2)^{1/4}}$$

$$\phi = \frac{2\pi n L \cos \theta}{\lambda}$$

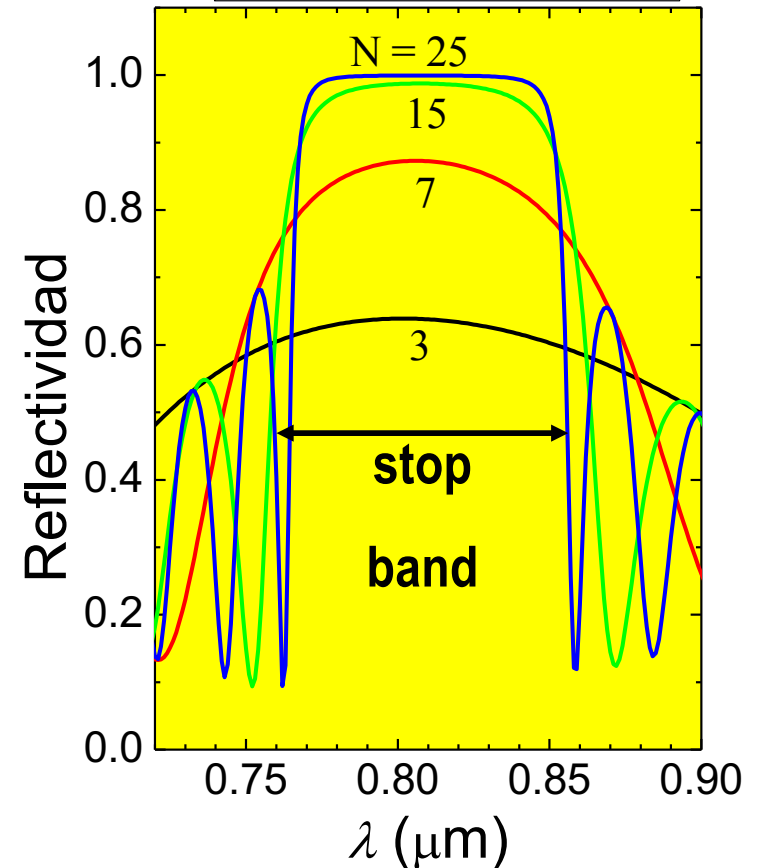
$$Q \propto F = \frac{\Delta \nu_{fsr}}{\Delta \nu_c} = \frac{\pi (R_1 R_2)^{1/4}}{1 - \sqrt{R_1 R_2}}$$

Laser cavity (II)

Distributed Bragg Reflectors (DBR)



$n_1 = 2.9364 \quad d_1 = 688 \text{ \AA}$
 $n_2 = 3.4075 \quad d_2 = 593 \text{ \AA}$

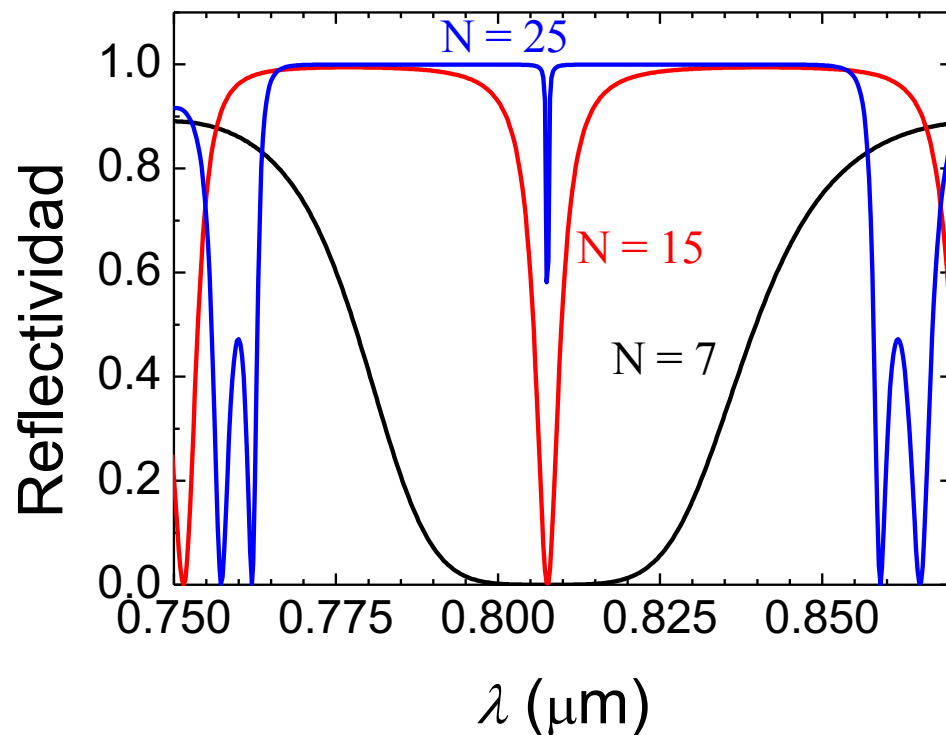


High reflectivity

- normal incidence
- many periods

Laser cavity (III)

- ➔ “Cavity” \longleftrightarrow open a region (d) in-between DBR
- ➔ “Defect” \longrightarrow increase of transmission ($R \downarrow$)
- ➔ $d = \lambda/2$ \longrightarrow transmission at the center of “stop”band

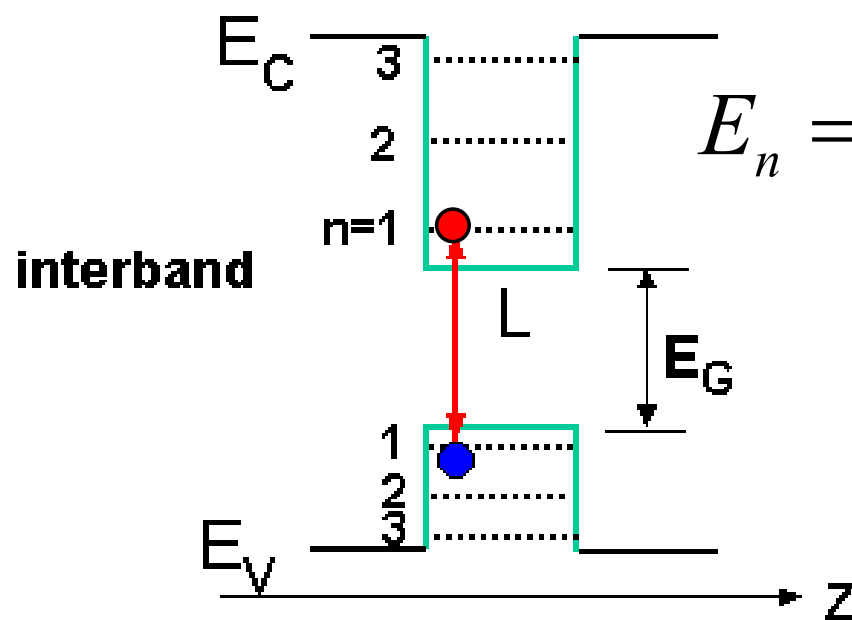


**Emitter
in the cavity**

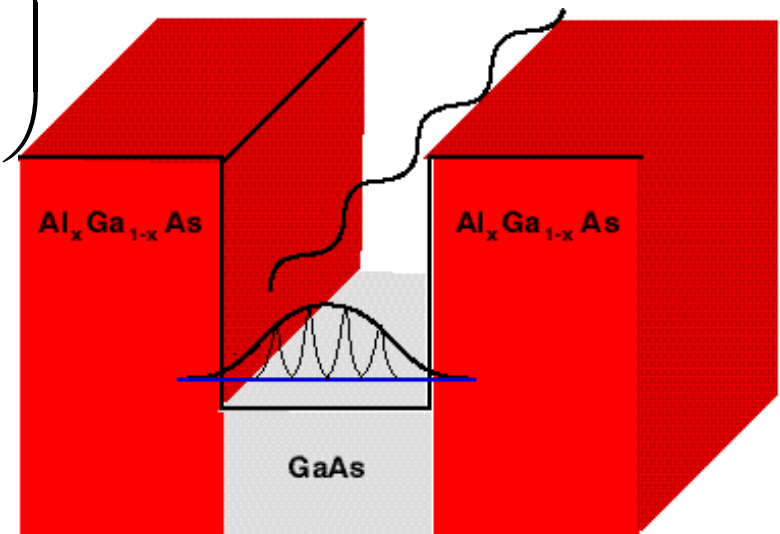
Emitter (I)

Quantum wells

- ➔ Artificial structures
- ➔ Layers ~10 nm, with different “gap”
- ➔ Quantum confinement effects

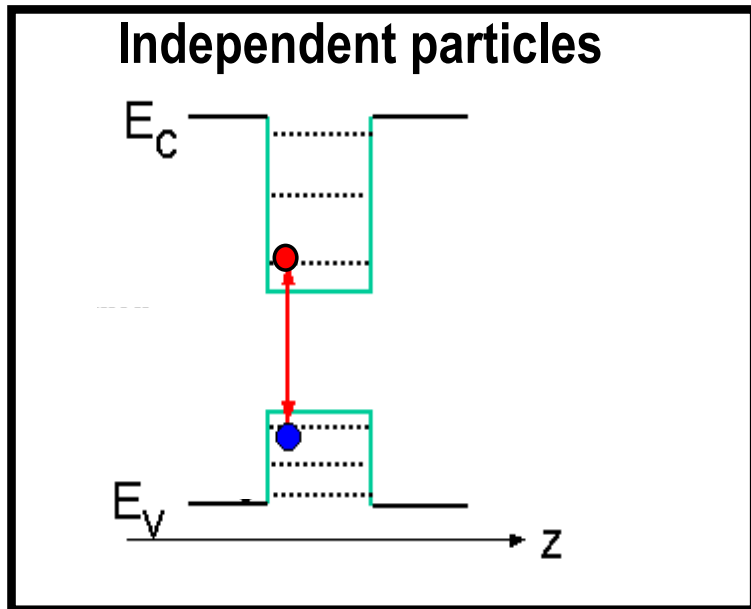


$$E_n = \frac{\hbar^2}{2m} \left(\frac{n\pi}{L} \right)^2$$



Emitter (II)

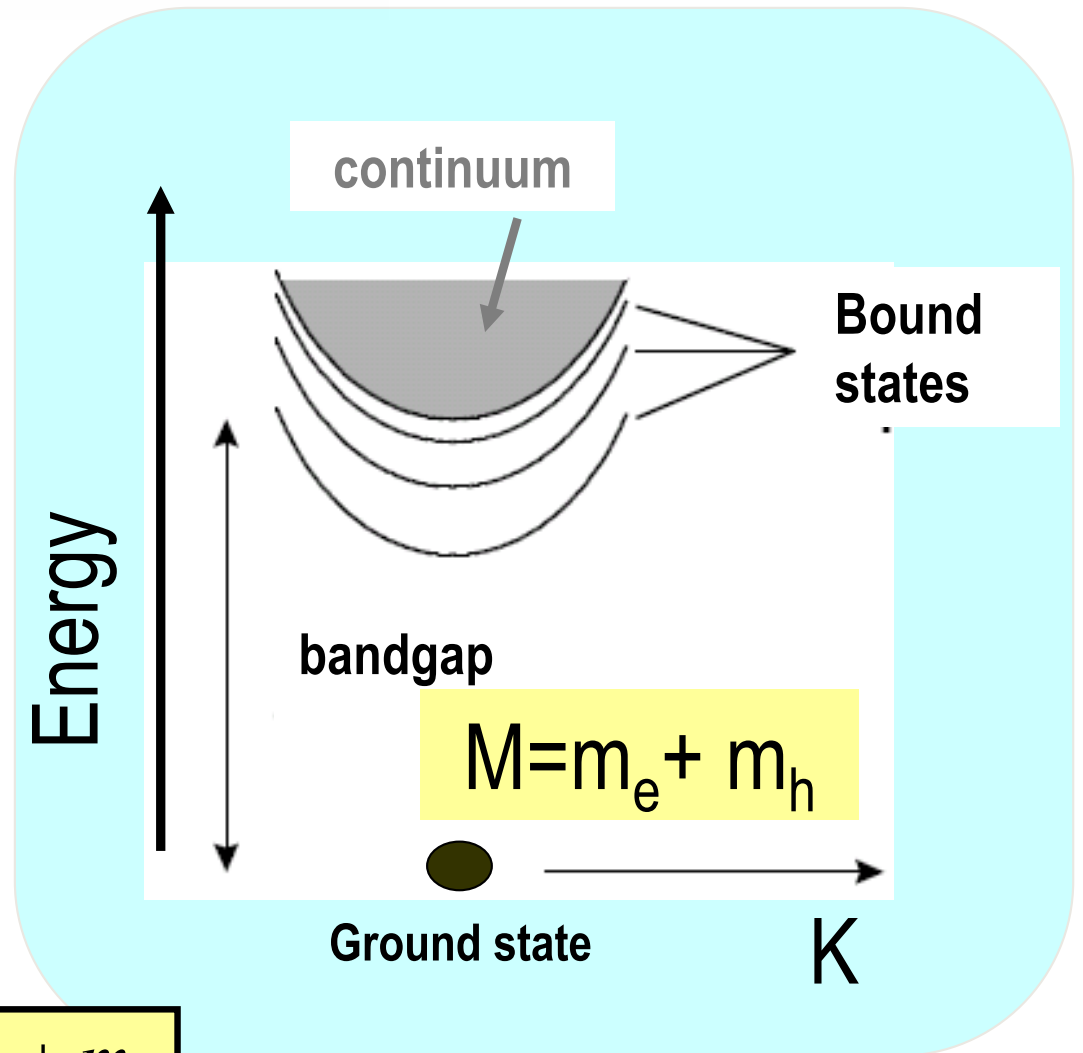
Excitons



Coulomb interaction

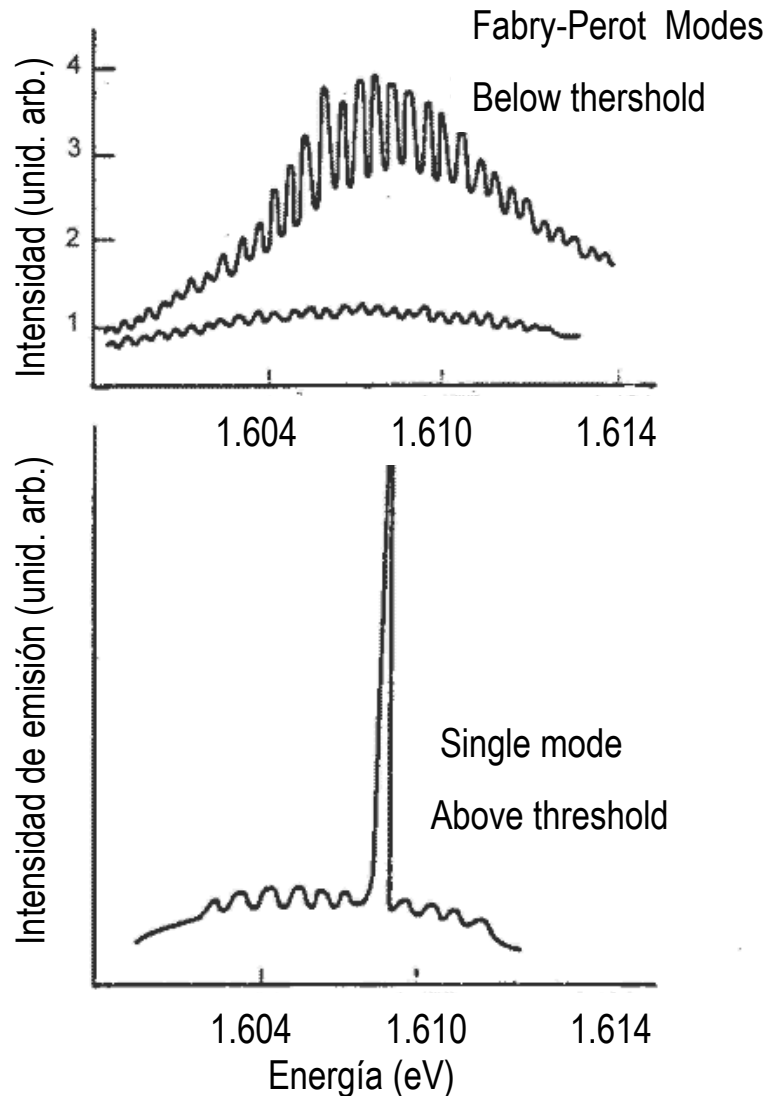
$$-\frac{e^2}{4\pi\epsilon_r\epsilon_o|\vec{r}_e - \vec{r}_h|}$$

$$\mu = \frac{m_e + m_h}{m_e \times m_h}$$



Integer Spin \rightleftarrows **Boson**

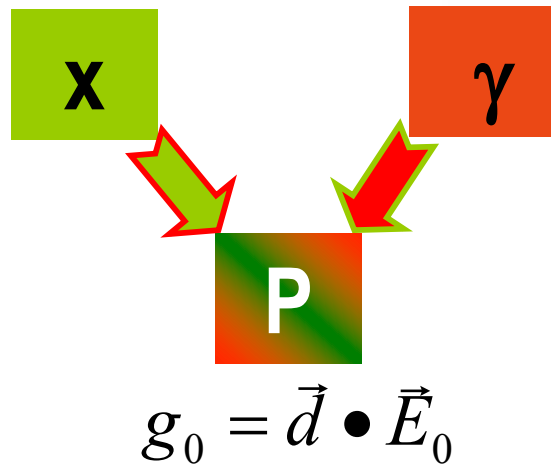
VCSEL



- Weak coupling
- ➔ Fast damping rates
 - ➔ Irreversible emission decay
 - ➔ Mode crossing

**Modification of
spontaneous decay rates**

Exciton-Polariton (I)



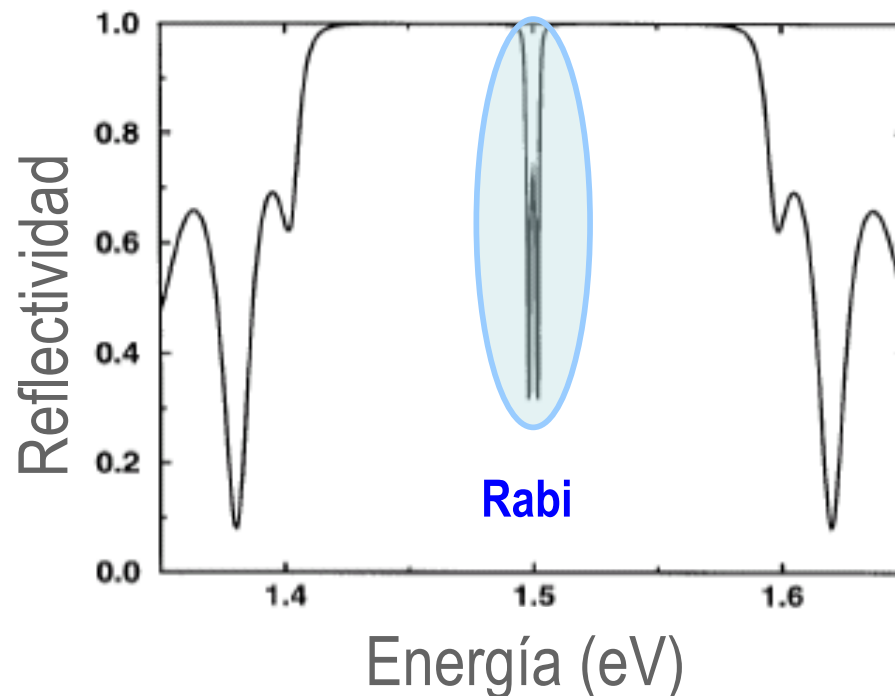
Integer Spin



Boson

Strong coupling

- ➔ Slow damping rates
- ➔ Oscillations $|X, \gamma\rangle \leftrightarrow |\gamma, X\rangle$
- ➔ Mode anticrossing \rightarrow Rabi



Theory of the Contribution of Excitons to the Complex Dielectric Constant of Crystals*†

J. J. HOPFIELD‡

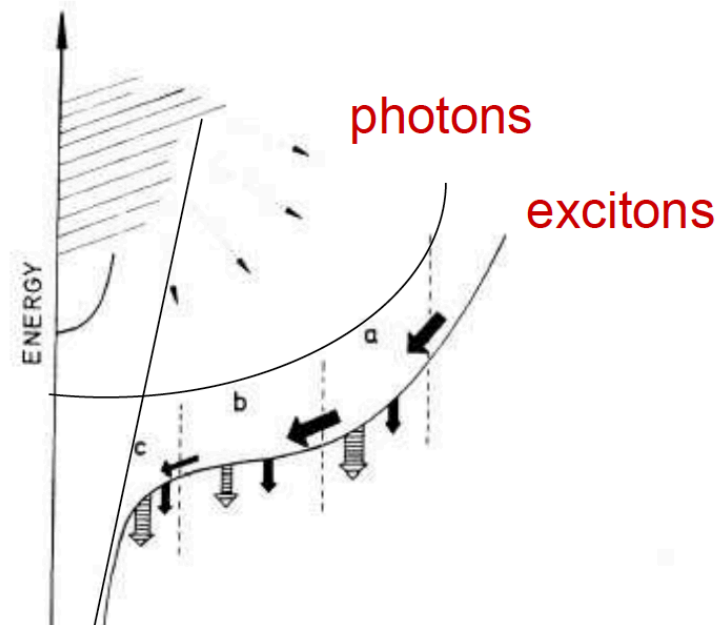
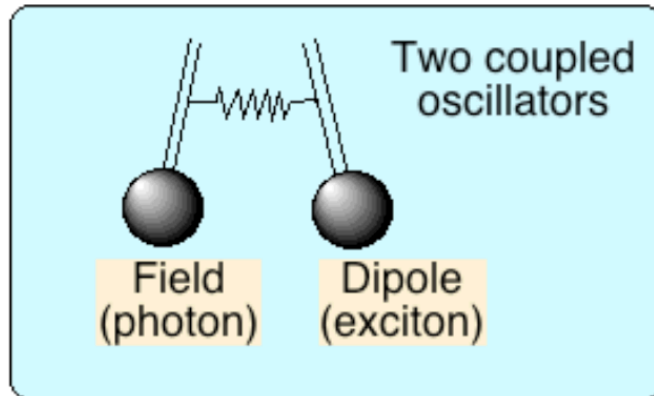
Physics Department, Cornell University, Ithaca, New York

(Received July 16, 1958)

It is shown that the ordinary semiclassical theory of the absorption of light by exciton states is not completely satisfactory (in contrast to the case of absorption due to interband transitions). A more complete theory is developed. It is shown that excitons are approximate bosons, and, in interaction with the electromagnetic field, the exciton field plays the role of the classical polarization field. The eigenstates of the system of crystal and radiation field are mixtures of photons and excitons. The ordinary one-quantum optical lifetime of an excitation is infinite. Absorption occurs only when "three-body" processes are introduced. The theory includes "local field" effects, leading to the Lorentz local field correction when it is applicable. A Smakula equation for the oscillator strength in terms of the integrated absorption constant is derived.

Strongly-coupled 3D excitons and photons, excitonic polaritons are the quasi particles of the system

Exciton $\omega.k$ \longleftrightarrow photon $\omega.k$

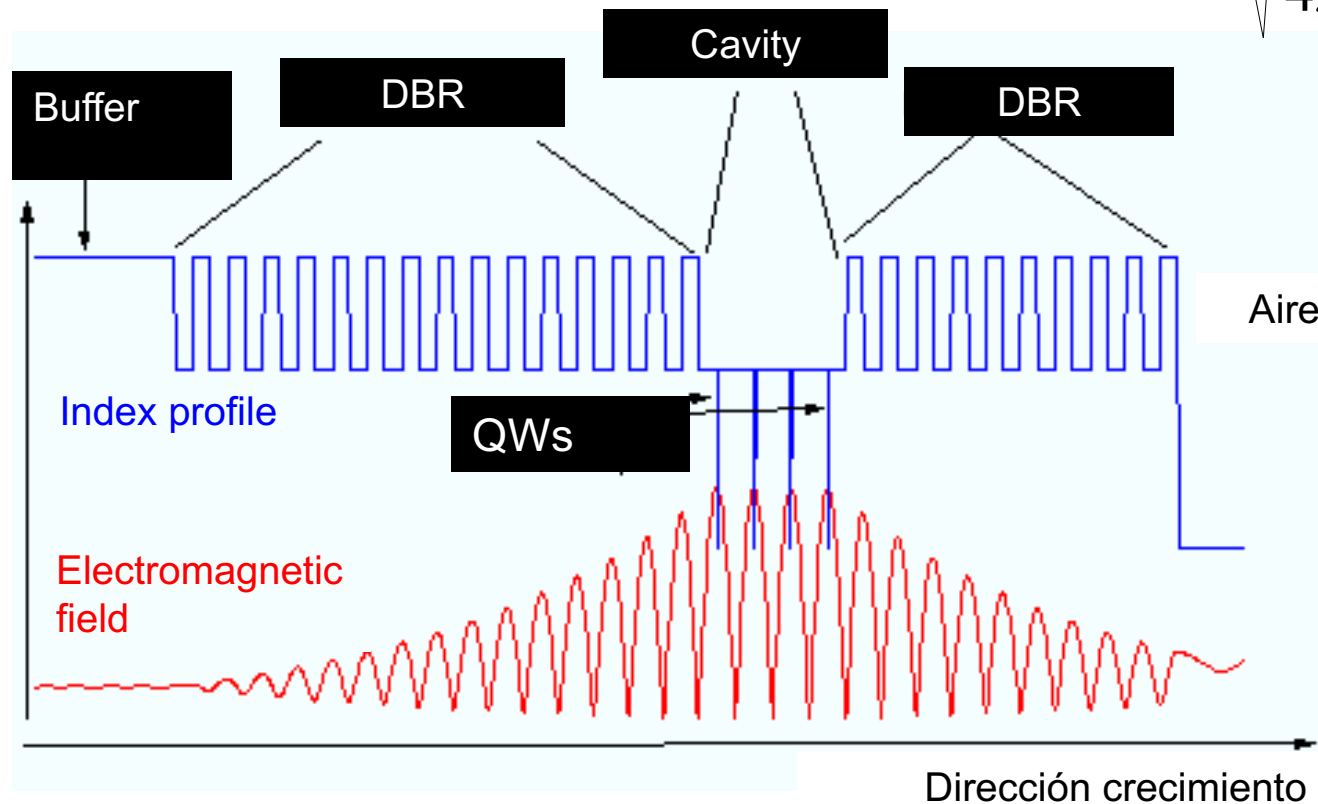


Exciton-Polariton (II)



Light-matter interaction optimization

$$\Omega = 2 \sqrt{\frac{e^2}{4\pi\epsilon_0\epsilon_r} \frac{2\pi}{m_0} N f_X L_{eff}}$$



Position

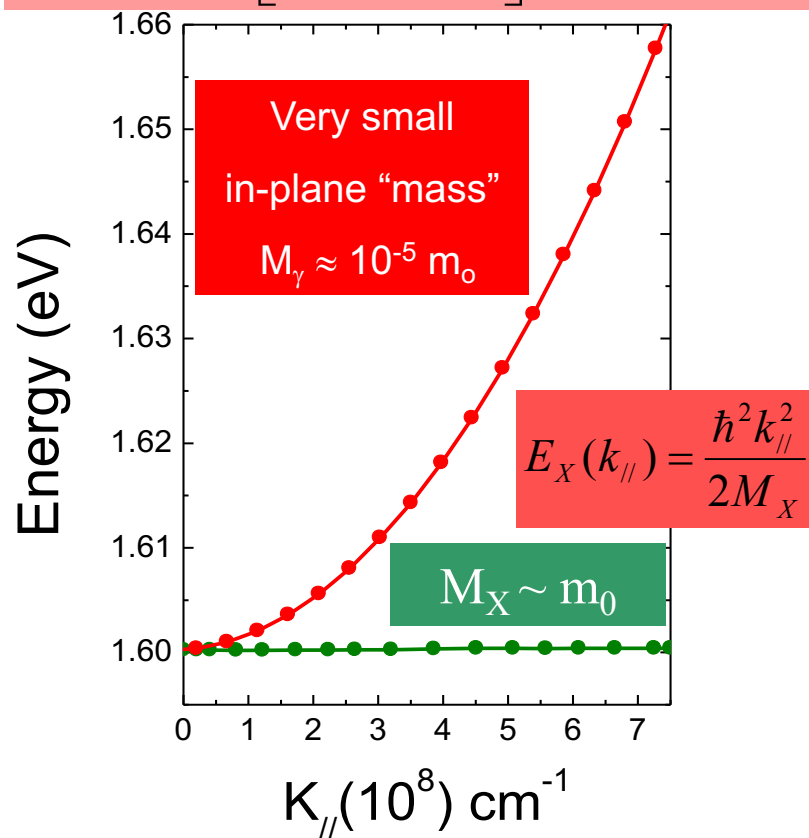
Dispersion relations

Along the growth direction (confinement):

$$k_z = 2\pi/L$$

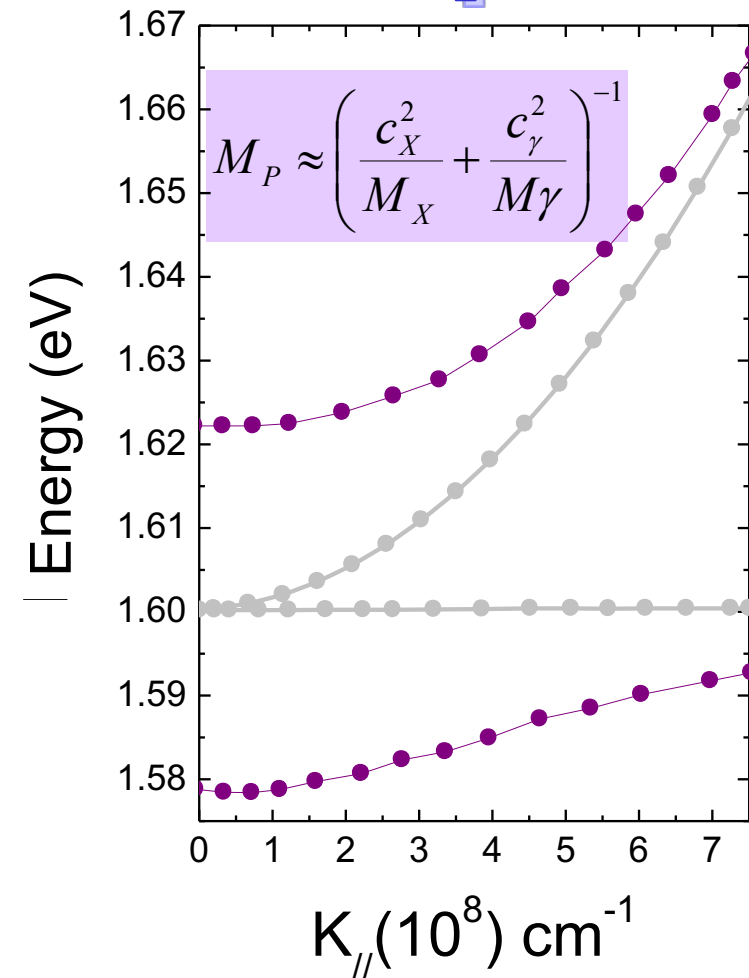
Decoupled

$$E_\gamma(k_{//}) = \frac{\hbar c}{n} \left[\left(\frac{2\pi}{L} \right)^2 + k_{//}^2 \right]^{1/2} = E_0 \left(1 + \frac{\hbar^2 c^2 k_{//}^2}{E_0^2 n^2} \right)^{1/2}$$

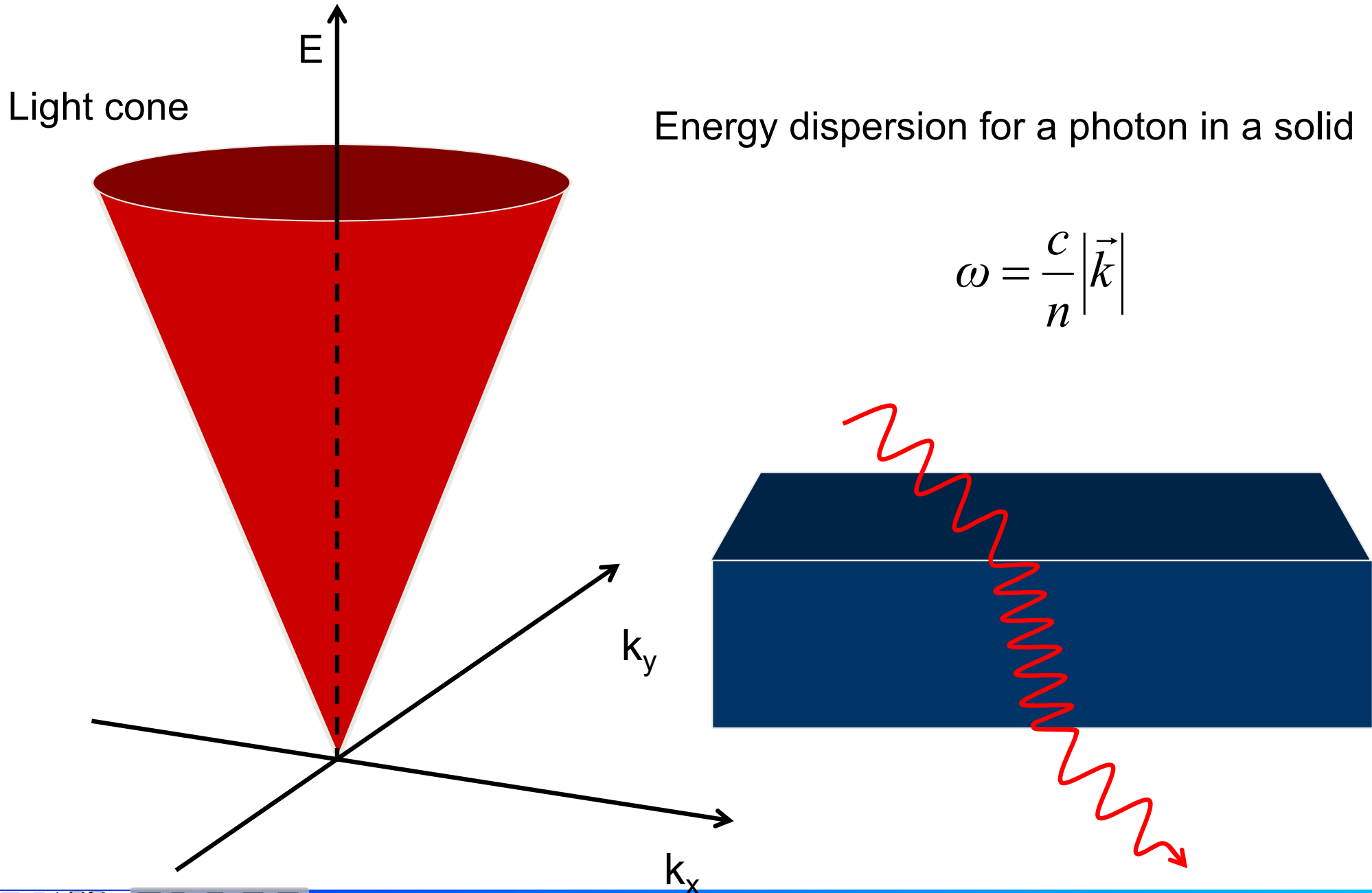


$$K_{//} = \frac{E}{\hbar c} \sin \theta$$

Coupled



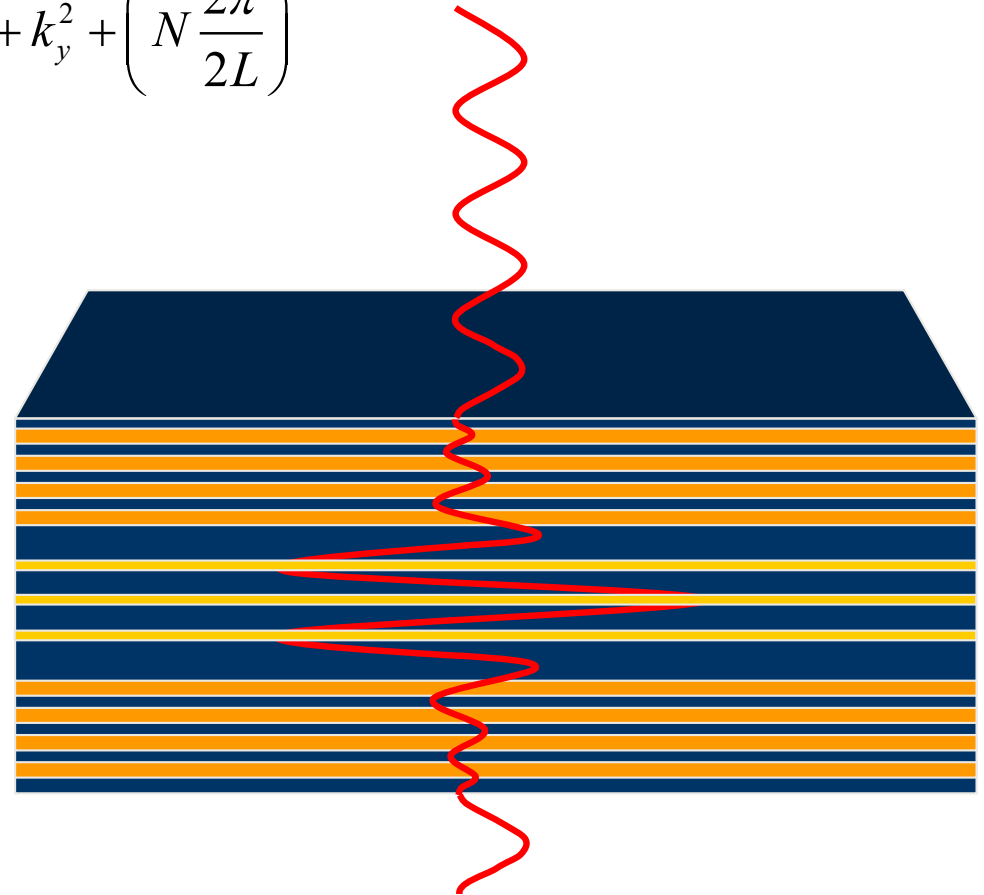
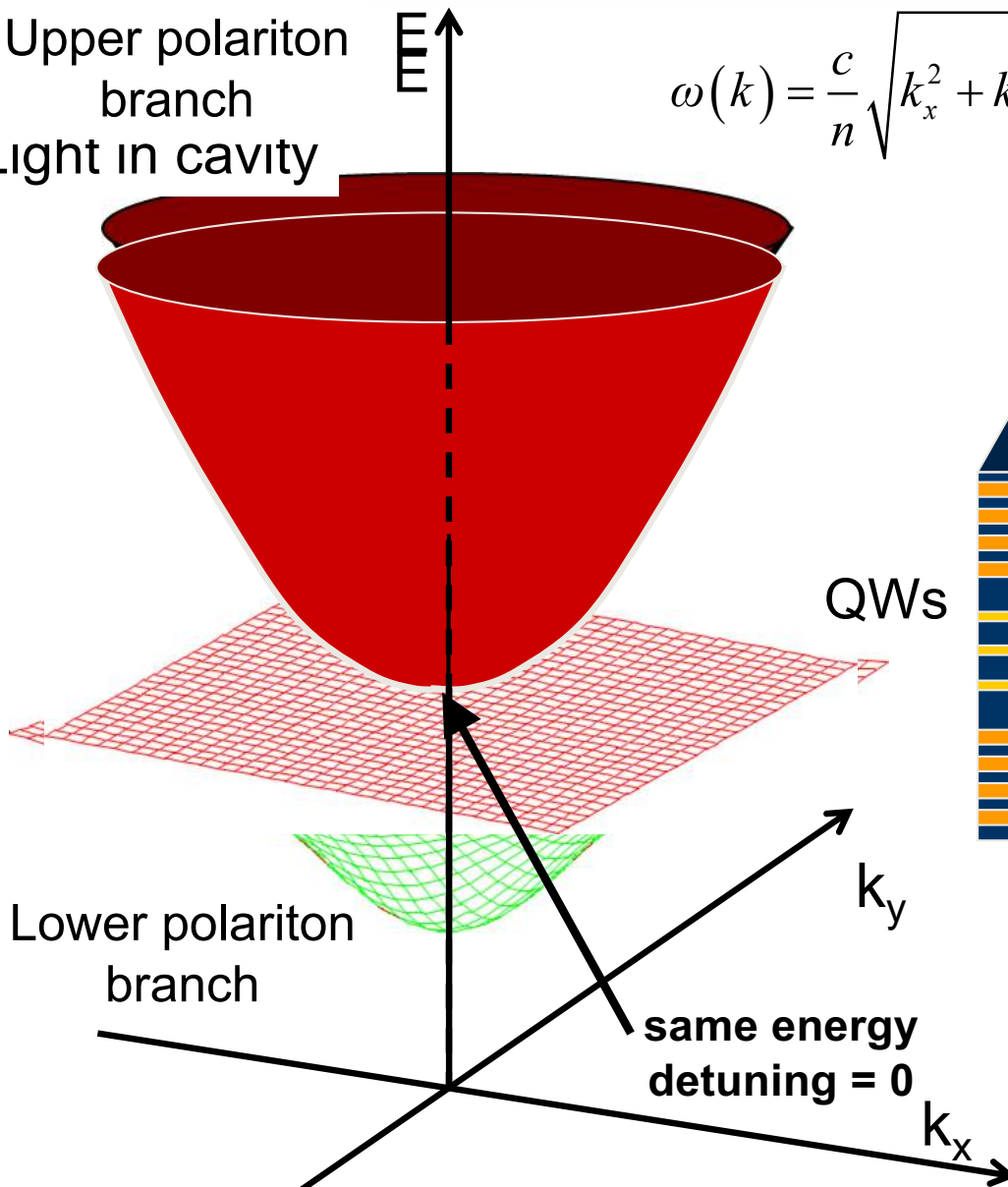
Semiconductor microcavities



Semiconductor microcavities

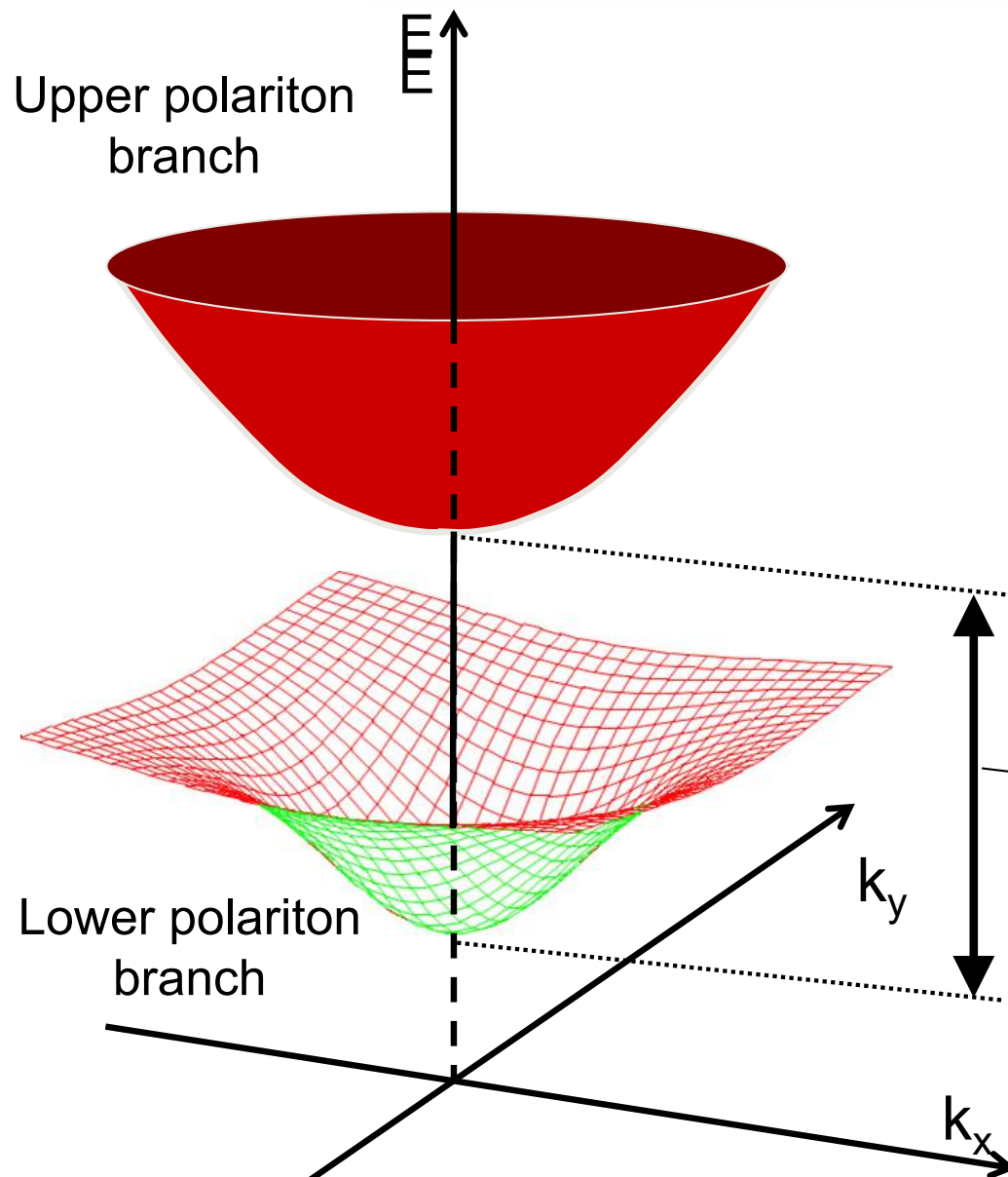
Upper polariton branch
Light in cavity

$$\omega(k) = \frac{c}{n} \sqrt{k_x^2 + k_y^2 + \left(N \frac{2\pi}{2L}\right)^2}$$



$$\mathcal{H}_{pol}(k_{\parallel}) = \begin{pmatrix} \hbar\omega_c(k_{\parallel}) & \hbar\Omega_R \\ \hbar\Omega_R & \hbar\omega_x(k_{\parallel}) \end{pmatrix}$$

Semiconductor microcavities



Strong exciton confinement
Enhanced electromagnetic field



Strong light-matter coupling

New eigenstates
POLARITONS

$$\hat{Q}_{UPB} = c \cdot \hat{P} + d \cdot \hat{X}$$

$$\hat{Q}_{LPB} = -d \cdot \hat{P} + c \cdot \hat{X}$$

Rabi splitting

$$\Omega_R^2 = \frac{(1 + \sqrt{R})^2}{2\sqrt{R}} \frac{c\Gamma_0}{n_{cav}L_{eff}}$$

Low polariton mass

“S” shaped dispersion

Momentum trap

Polaritons

New eigenstates
POLARITONS

$$\hat{Q}_{UPB} = c \cdot \hat{P} + d \cdot \hat{X}$$

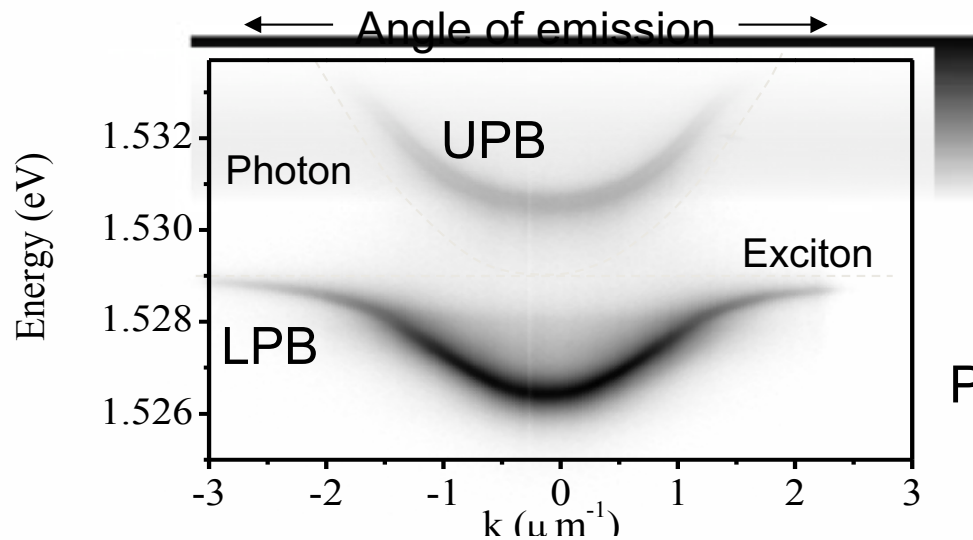
$$\hat{Q}_{LPB} = -d \cdot \hat{P} + c \cdot \hat{X}$$

Polaritons

New eigenstates
POLARITONS

$$\hat{Q}_{UPB} = c \cdot \hat{P} + d \cdot \hat{X}$$

$$\hat{Q}_{LPB} = -d \cdot \hat{P} + c \cdot \hat{X}$$



Polariton lifetime: 2-8 ps (at $k = 0$)

PL experiment

Polaritons

New eigenstates
POLARITONS

$$\hat{Q}_{UPB} = c \cdot \hat{P} + d \cdot \hat{X}$$

$$\hat{Q}_{LPB} = -d \cdot \hat{P} + c \cdot \hat{X}$$

photonic content ↔ very low mass

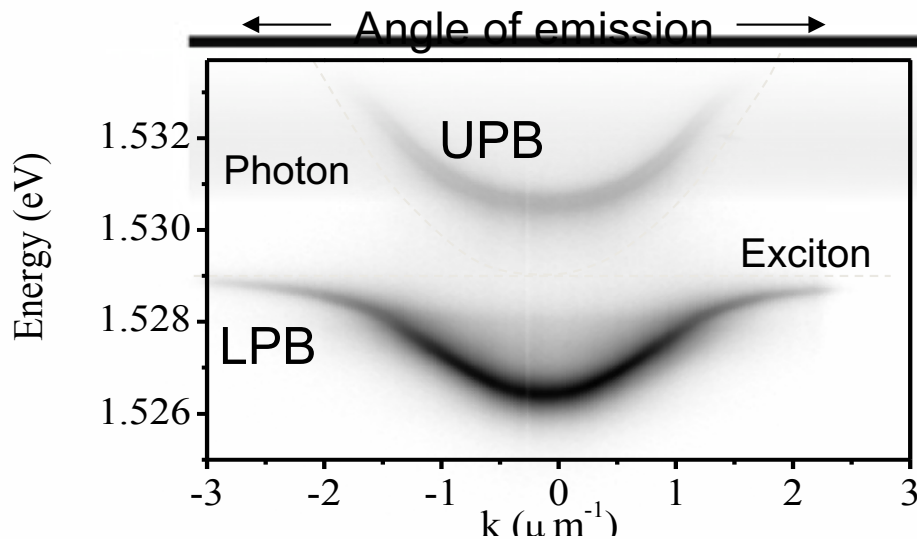


High condensation temperature

10 K - 300 K

$$\lambda_T = \left(\frac{2\pi\hbar^2}{mk_B T} \right)^{\frac{1}{2}}$$

composite
BOSONS

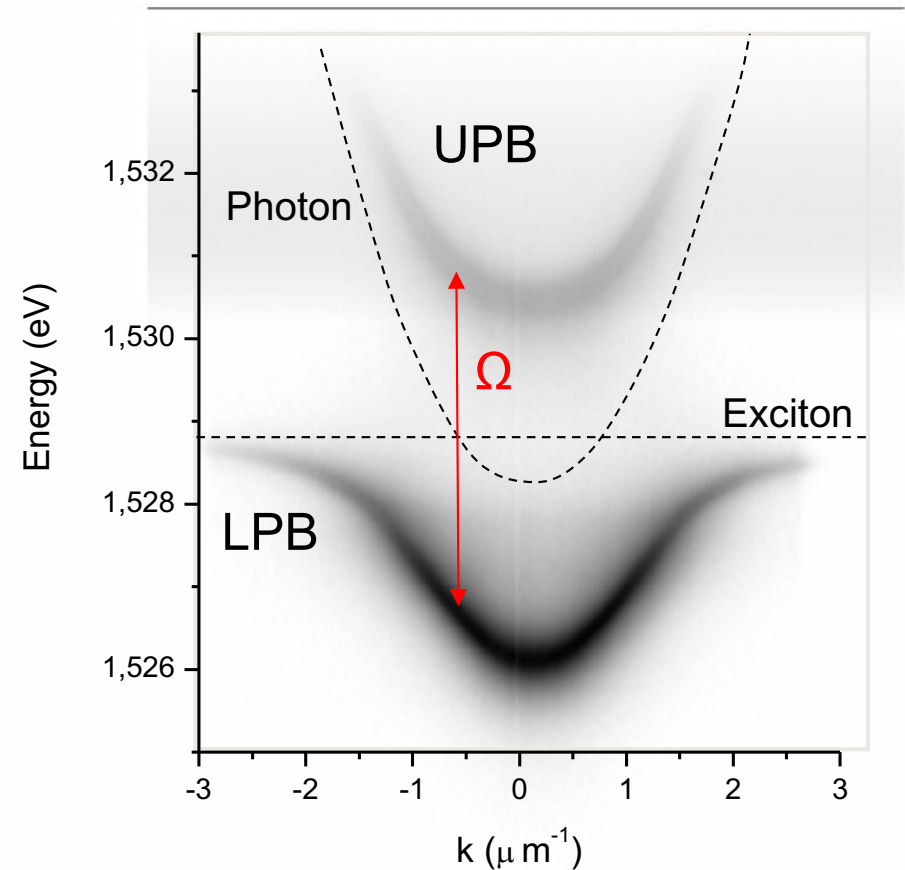
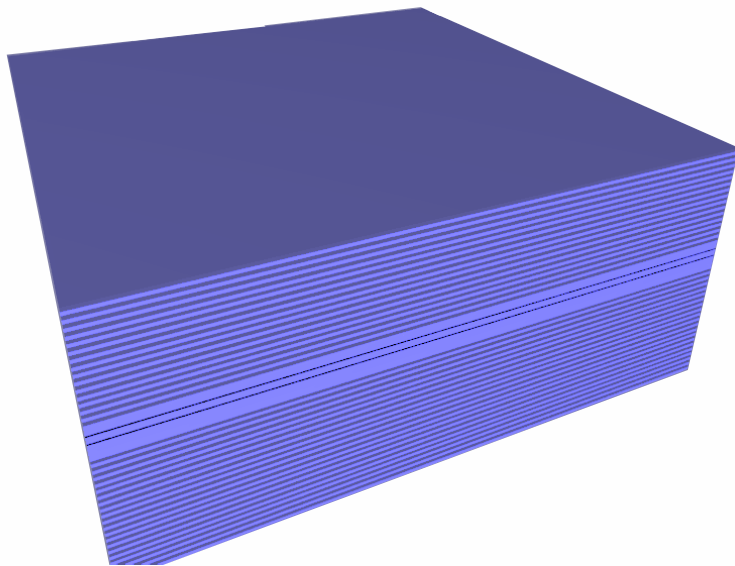


species	atomic gases	polaritons
mass m^*/m_0	10^4	10^{-5}
Bohr radius	10^{-1} \AA	10^2 \AA
λ_T at T_c	10^3 \AA	10^4 \AA
T_c	$< 1 \mu\text{K}$	10 – 300K

Polariton lifetime: 2-8 ps (at $k = 0$)

PL experiment

Polaritons



• Low mass ($10^{-5} m_e$) \rightarrow low density of states

• Strong Rabi splitting (~ 3 meV) \rightarrow polariton ~ 30 meV $= \left(\frac{2\pi\hbar^2}{mk_B T} \right)^{\frac{1}{2}}$



GaAs

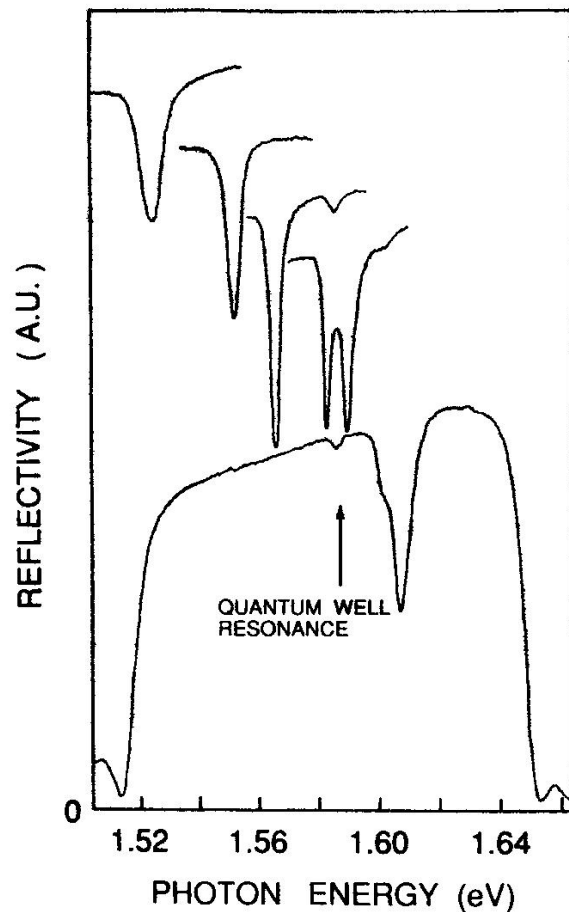
Ideal system to study interacting BEC

CdTe
High condensation temperatures
(10 K - 300 K)

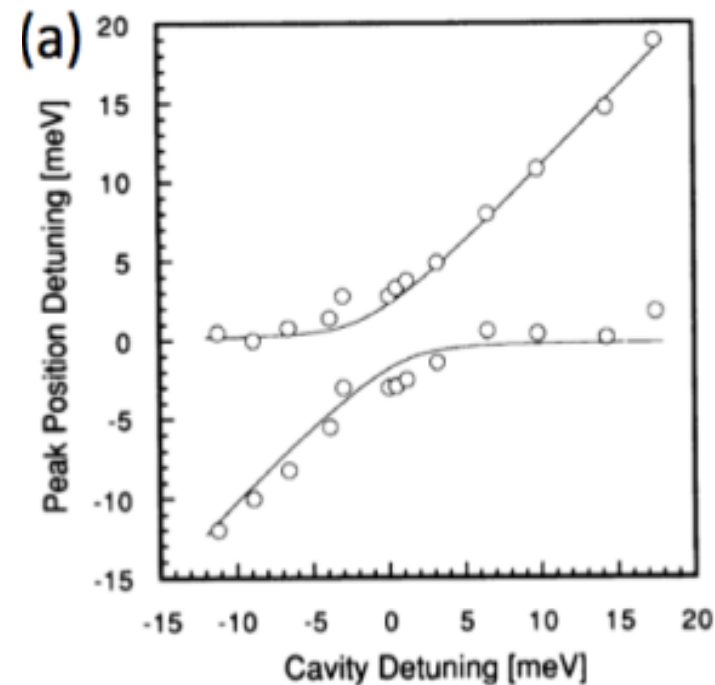
Some key studies

First report polaritons in microcavities

C. Weisbuch, *et al.*, Phys. Rev. Lett. **69**, 3314 (1992).



Changing the detuning

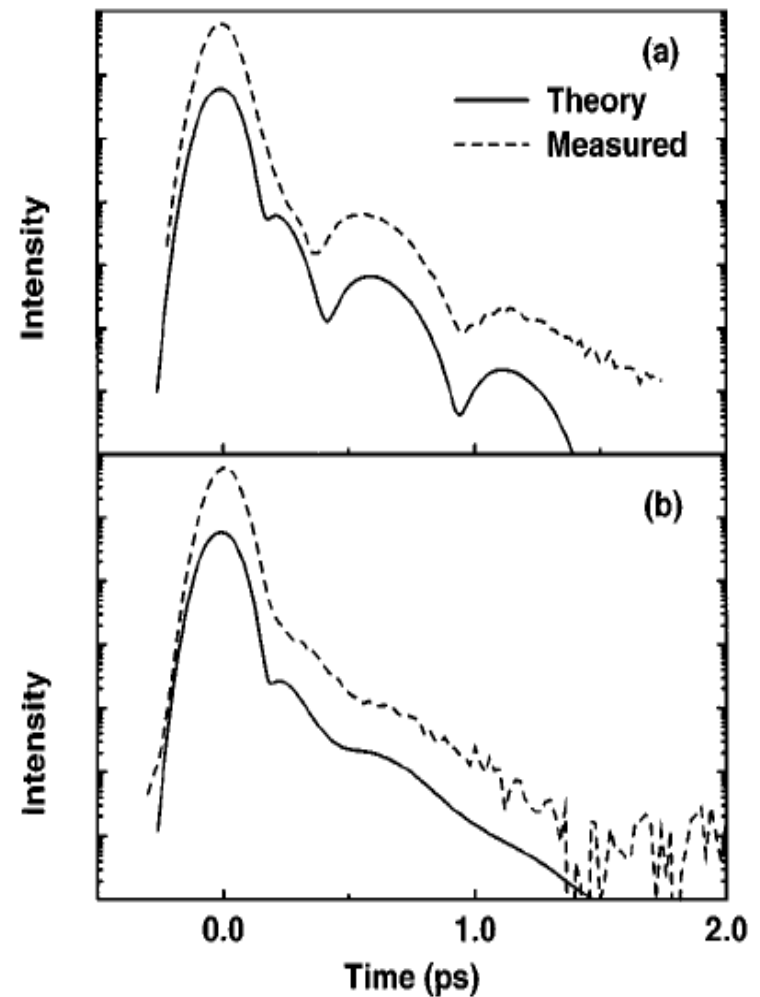
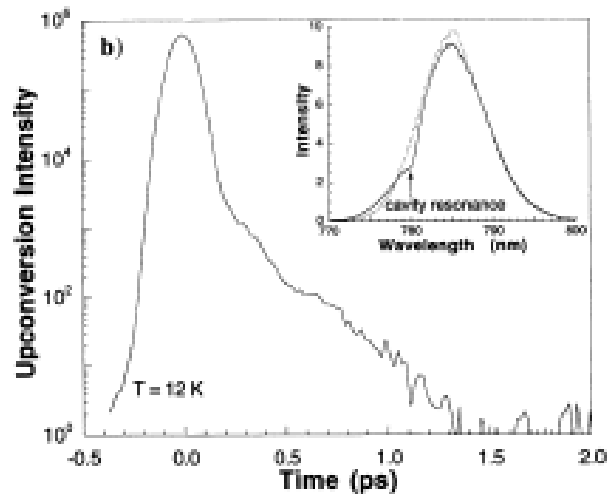
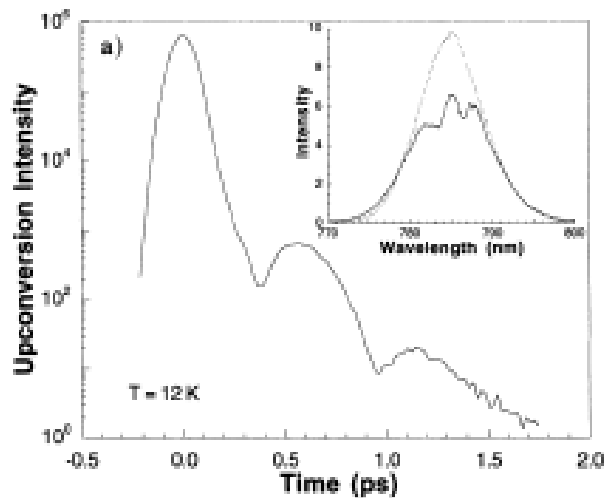


Some key studies

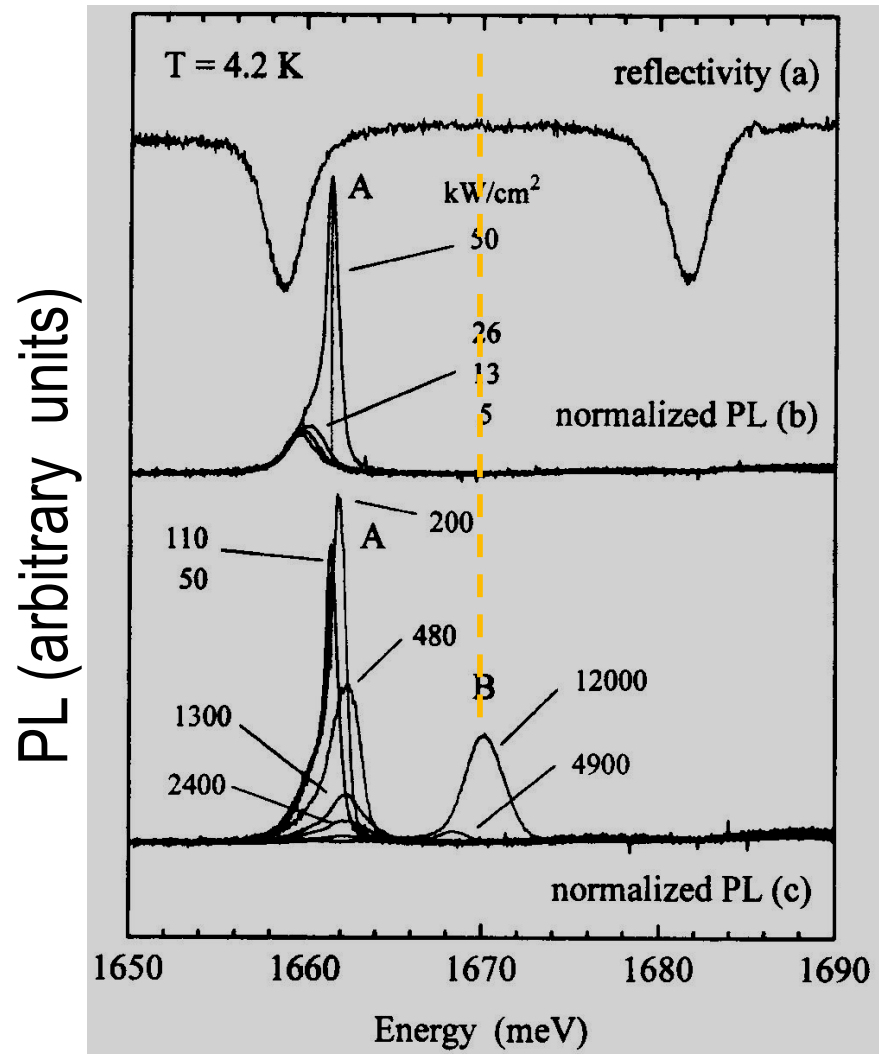
Vacuum Rabi oscillations

T. B. Norris, *et al.*, Phys. Rev. B **50**, 14663 (1994).

V. Savona & C. Weisbuch, Phys. Rev. B **54**, 10835 (1996)



Some key studies



PL in a non-linear regime

L.S. Dang et al., Phys. Rev. Lett. **81**, 3920 (1998)

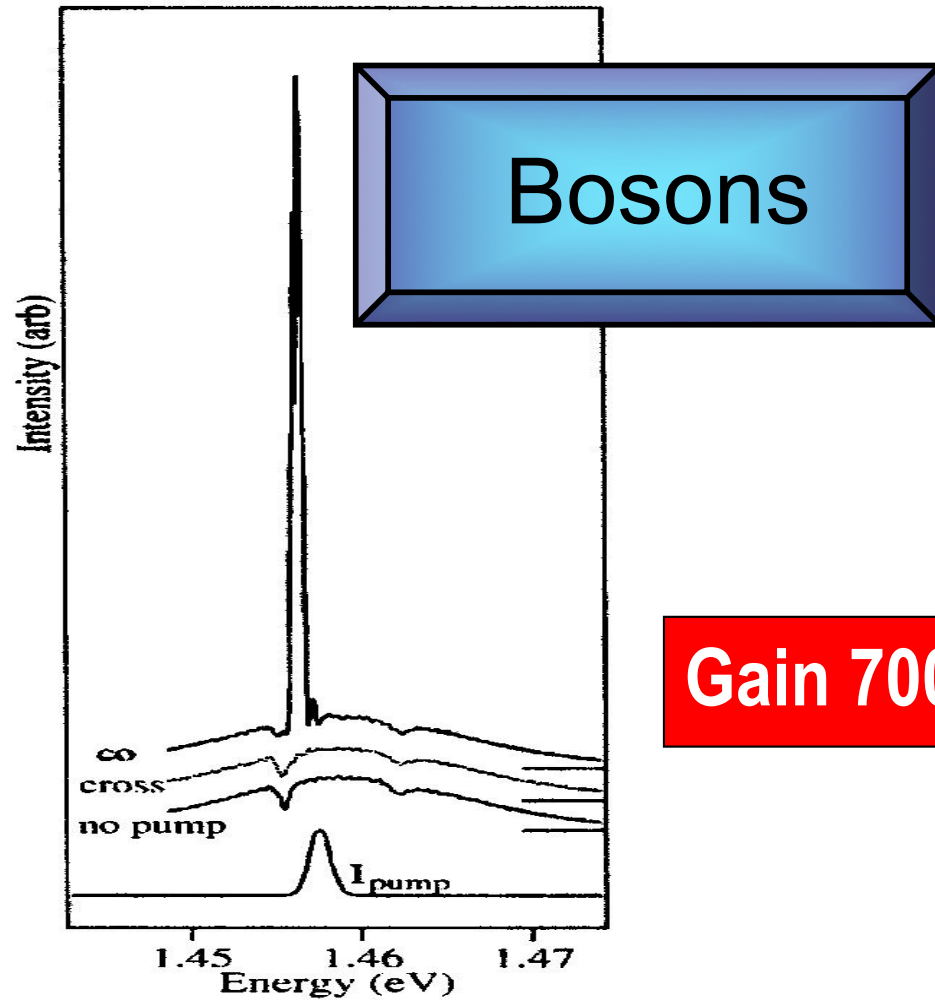
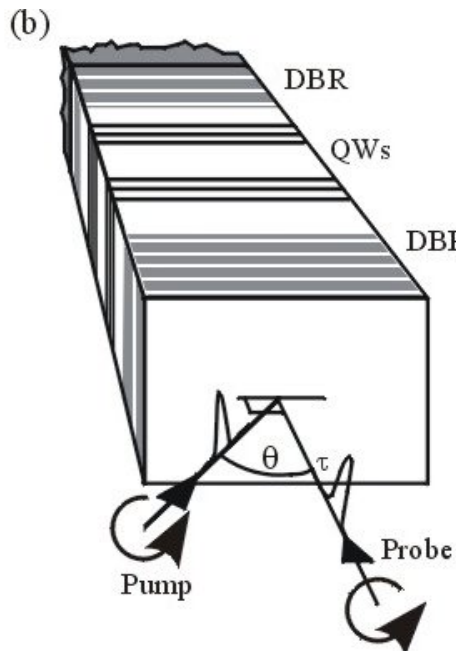
- ➡ Line narrowing
- ➡ Non-linear intensity increase

Some key studies

Amplification by stimulated polariton scattering

P.G. Savvidis et al. Phys. Rev. Lett. **84**, 1547 (2000)

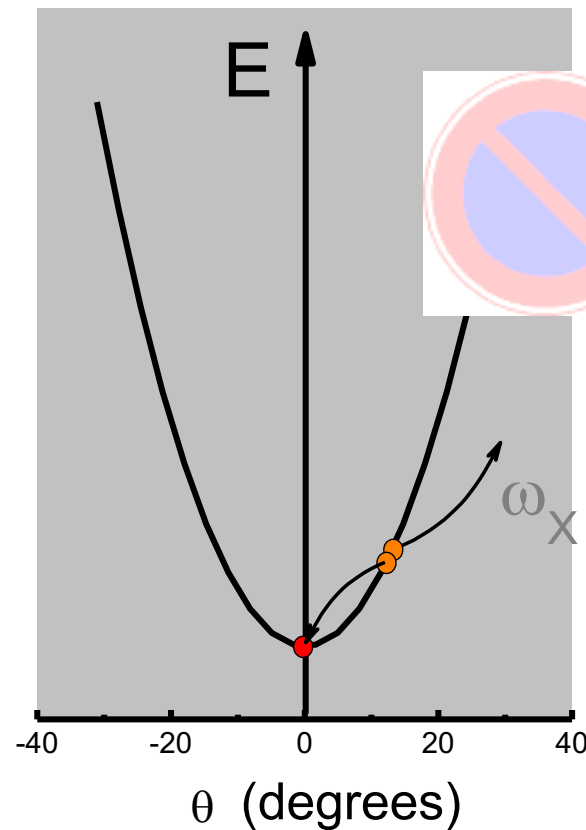
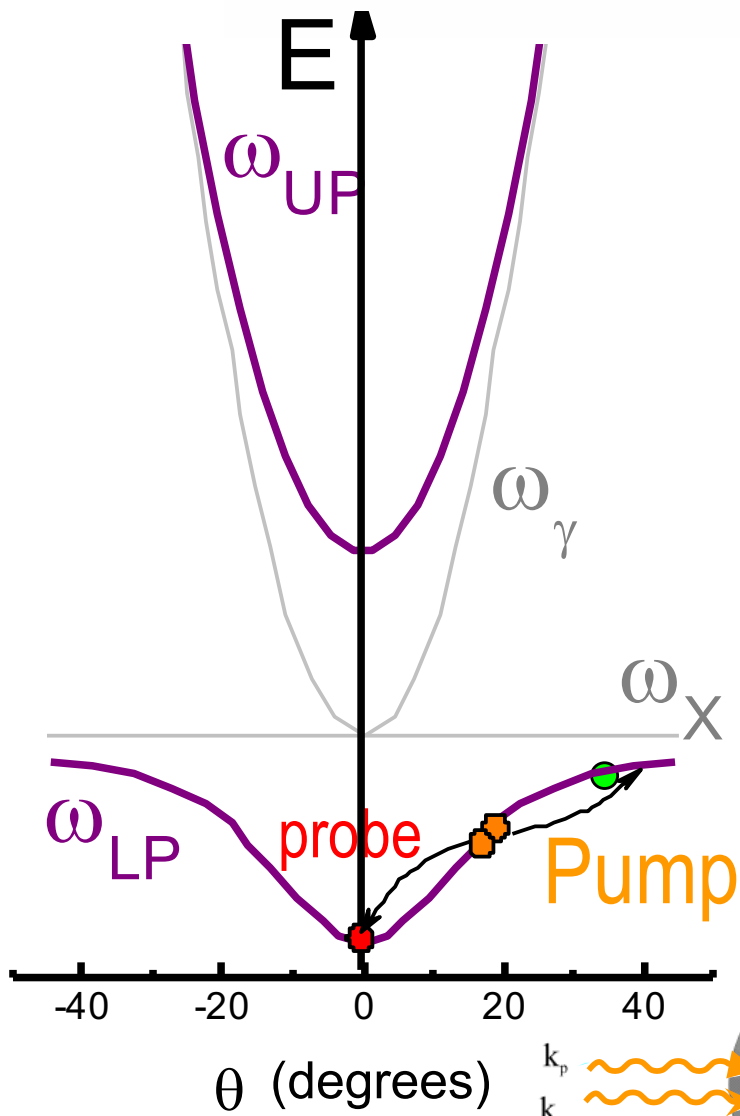
Reflectivity experiments:
“Pump & probe”



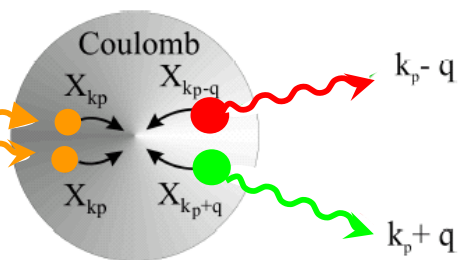
Gain 700%

Stimulated Scattering

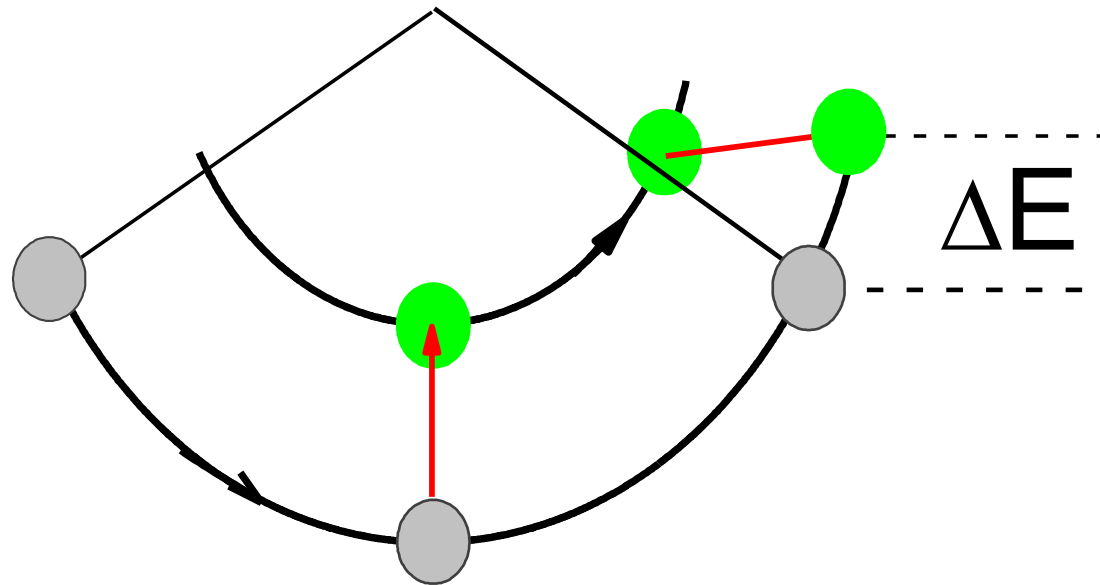
Polariton dispersion



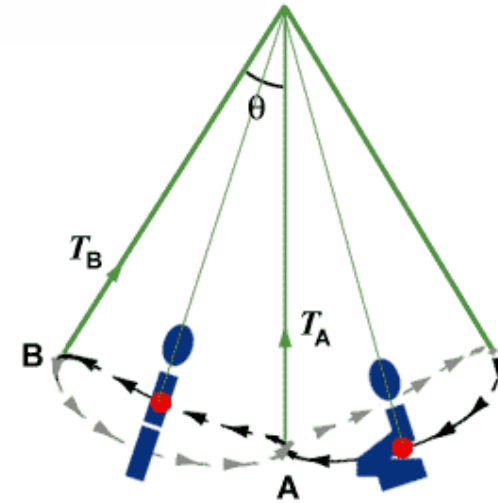
Exciton dispersion



Parametric Oscillator

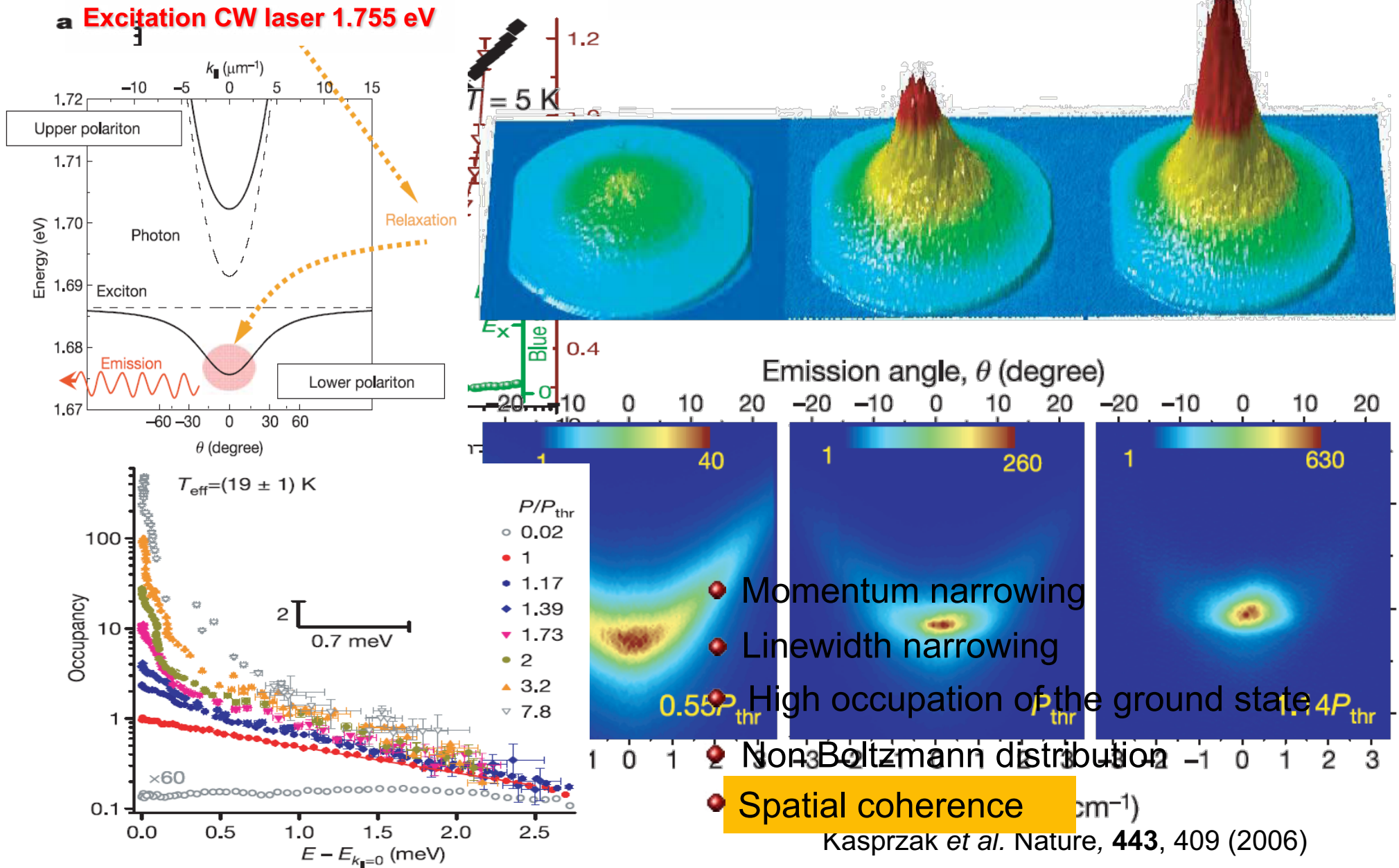


Pump



Some key studies

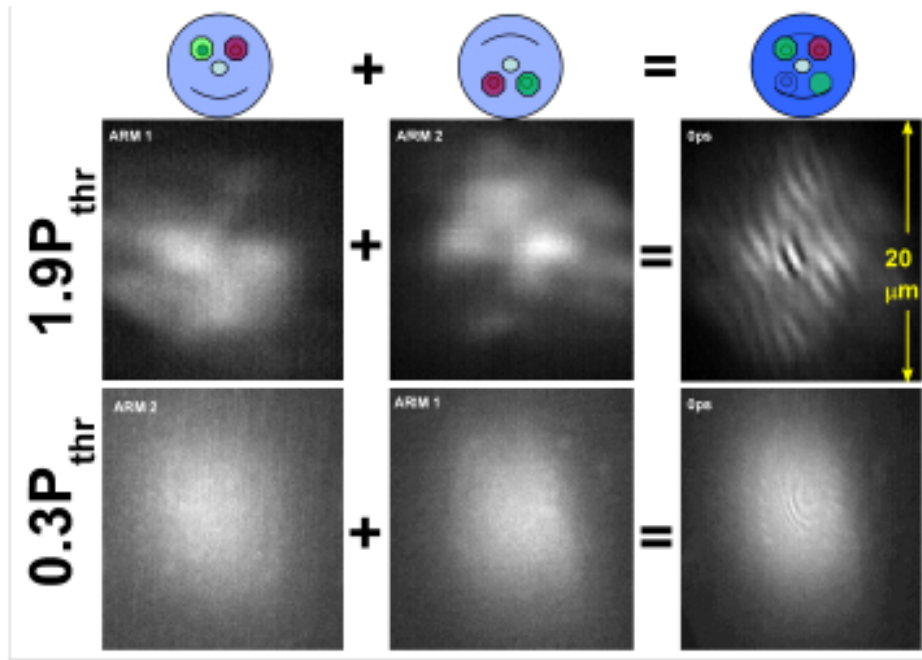
BEC of polaritons



Some key studies

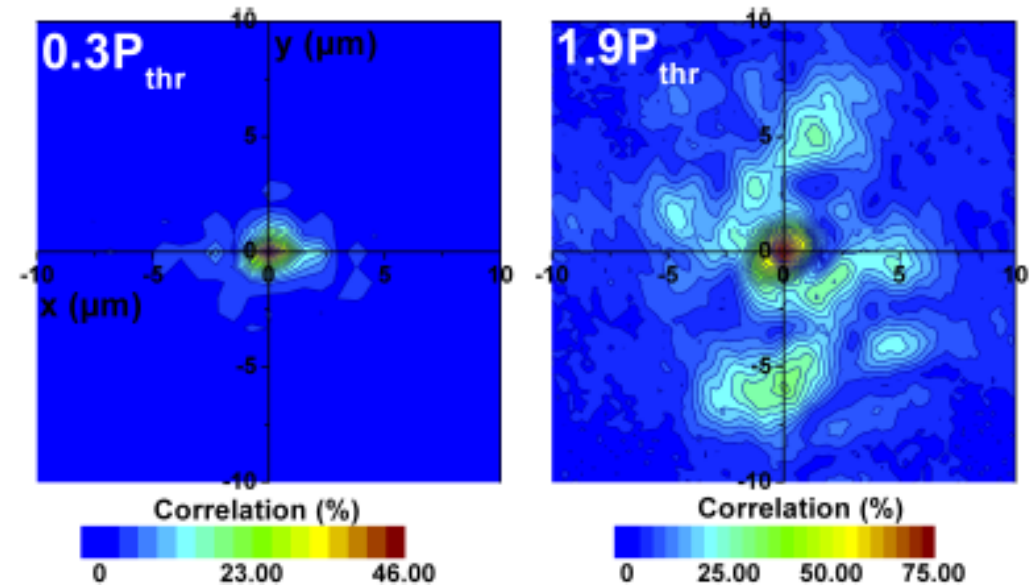
BEC of polaritons

• Spatial coherence



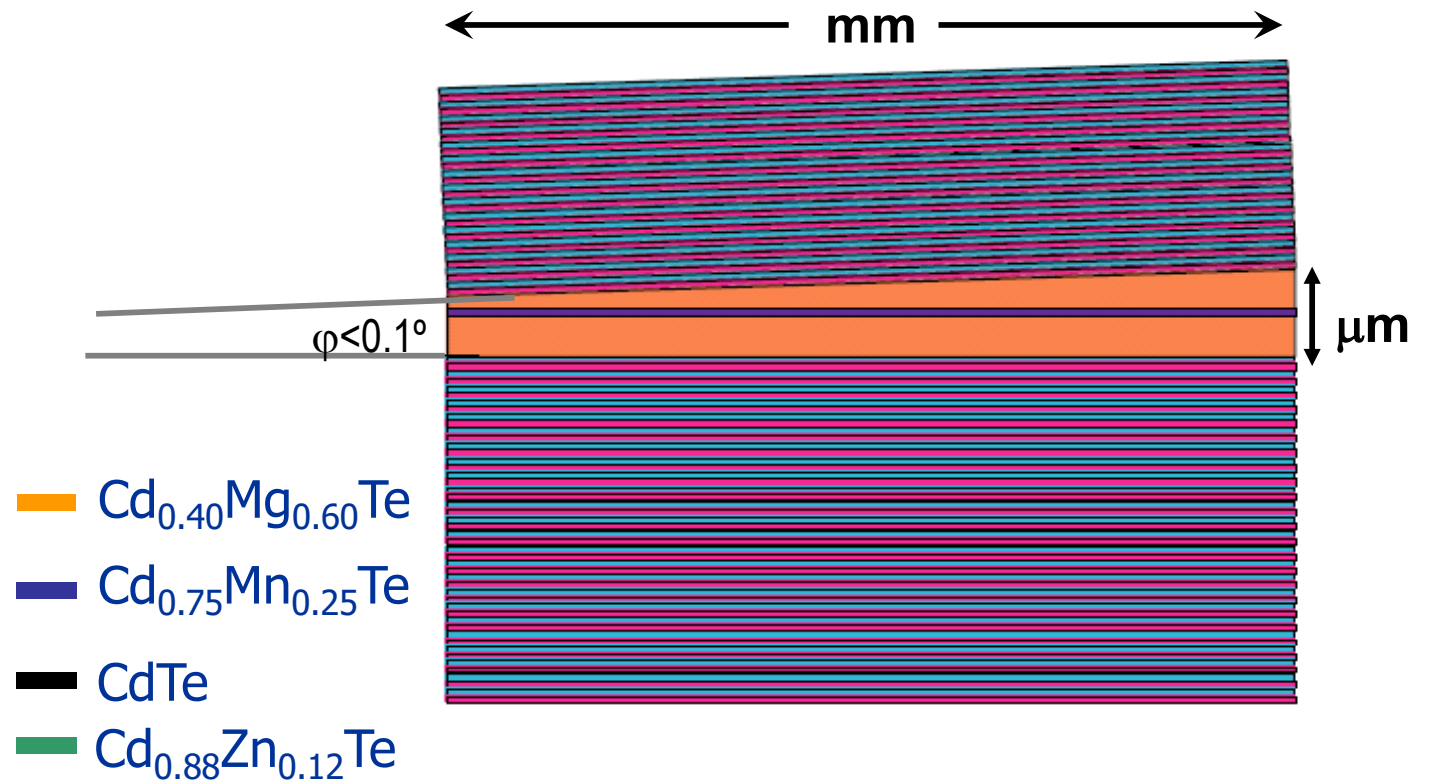
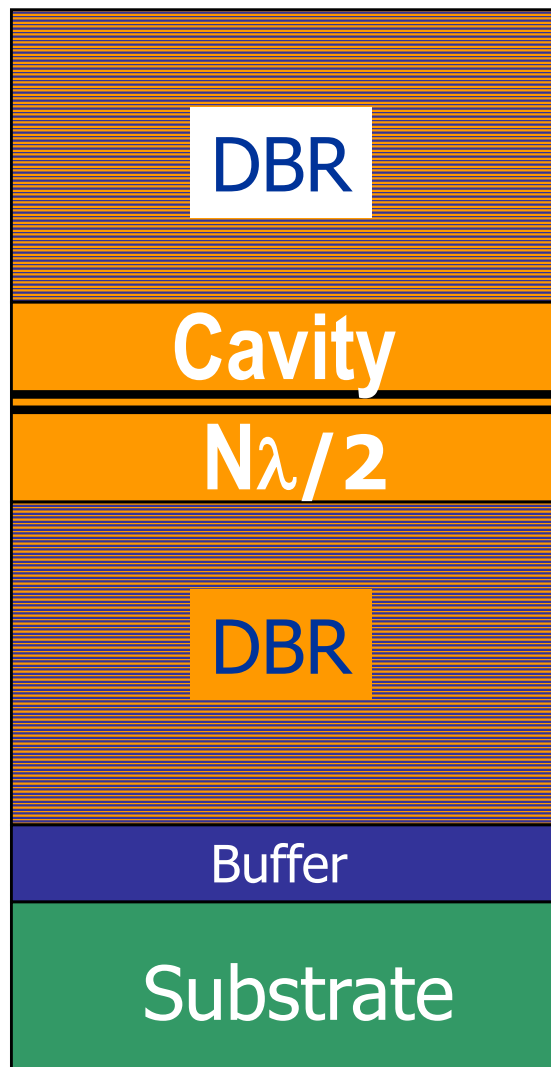
The principle of spatial correlation mapping using a Michelson interferometer

Kasprzak *et al.* Nature, **443**, 409 (2006)



Maps of the contrast of the spatial correlations

Key samples for condensation



- ➔ Adjust cavity length to exciton wavelength
- ➔ Change dispersion relation

Why CdTe?

⇒ Bosonic limit

$$\pi a_B^2 n_X \ll 1$$

$$a_B(\text{CdTe}) = 30 \text{ \AA}$$

<

$$a_B(\text{GaAs}) = 150 \text{ \AA}$$

$$n_X(\text{CdTe}) \sim 2 \times 10^{11} \text{ cm}^{-2}$$

>

$$n_X(\text{GaAs}) \sim 1 \times 10^{10} \text{ cm}^{-2}$$

⇒ Binding energies (polaritonic effects)

$$E_B(\text{CdTe}) = 25 \text{ meV}$$

>

$$E_B(\text{GaAs}) = 10 \text{ meV}$$

$$f_x(\text{CdTe}) = 2.3 \times 10^{13} \text{ cm}^{-2}$$

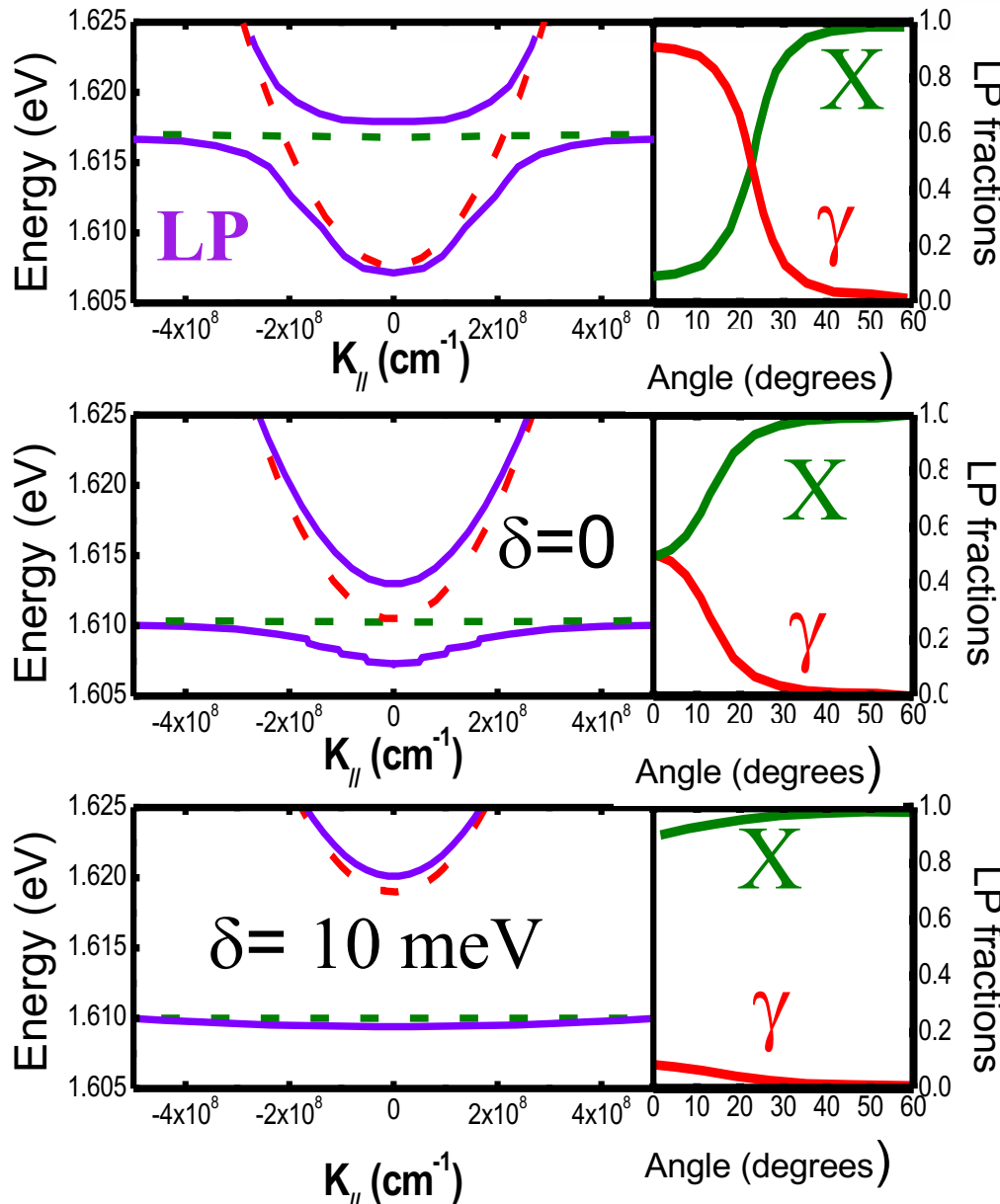
>

$$f_x(\text{GaAs}) = 0.6 \times 10^{13} \text{ cm}^{-2}$$

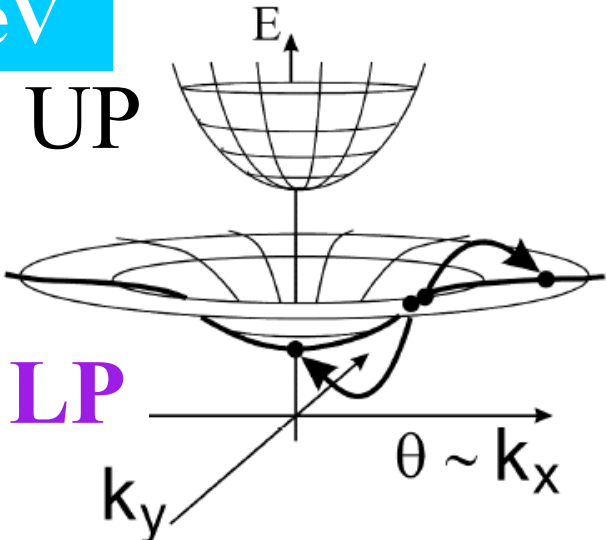
⇒ High temperatures

⇒ Epitaxial fabrication

Role of detuning (δ)



$\delta = -10 \text{ meV}$

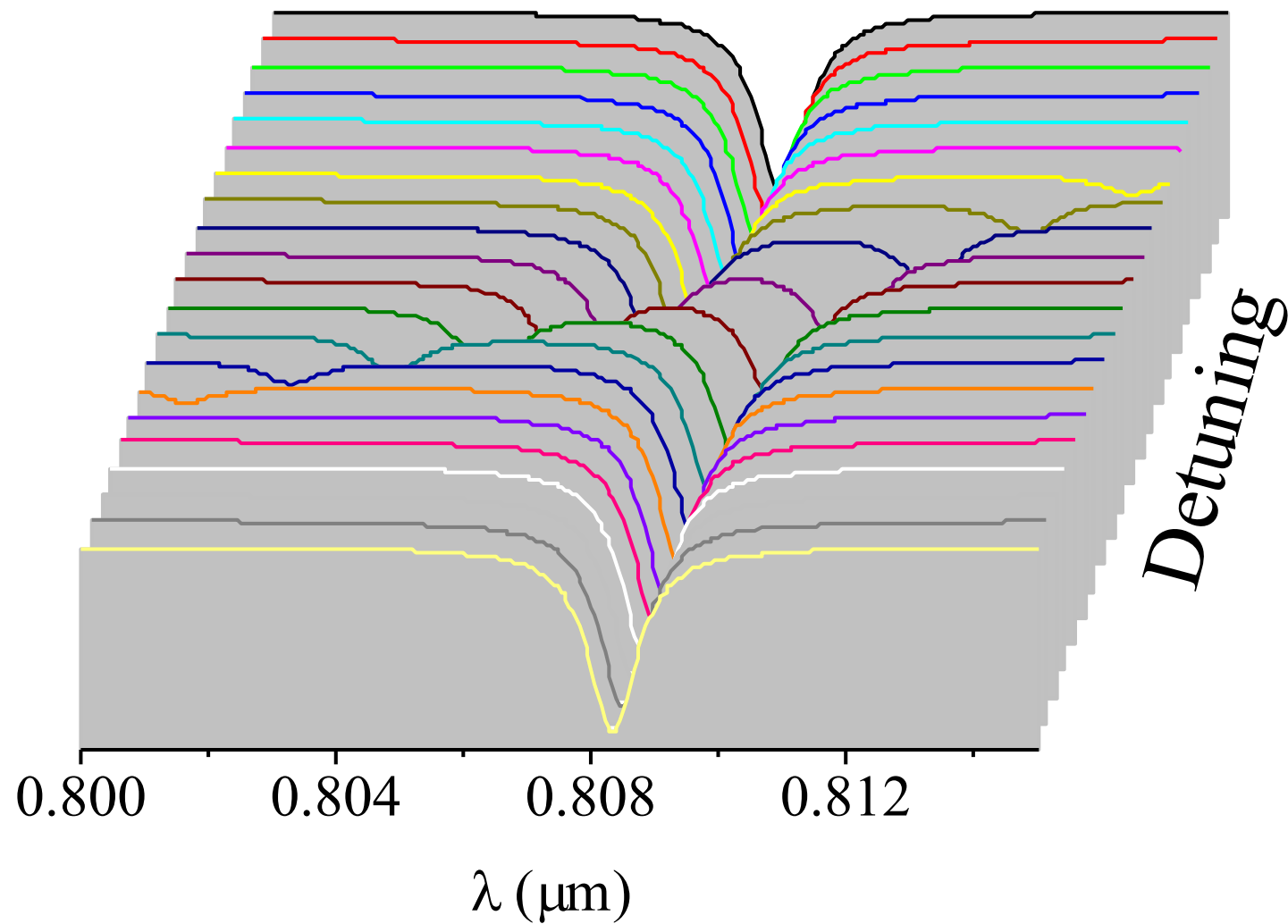


Polariton trap

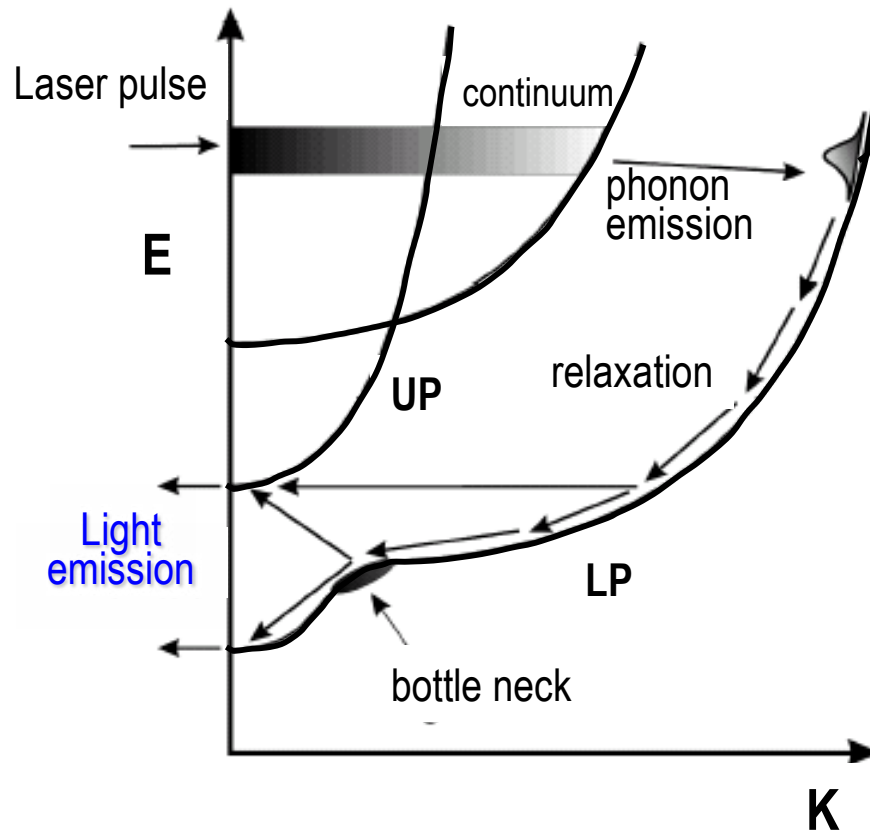
Depth $\Leftrightarrow \Omega$
 Extension $\Leftrightarrow \Delta k = \frac{\sqrt{3\epsilon\omega_x\Omega}}{c}$

Density of states \downarrow

Role of detuning (II)

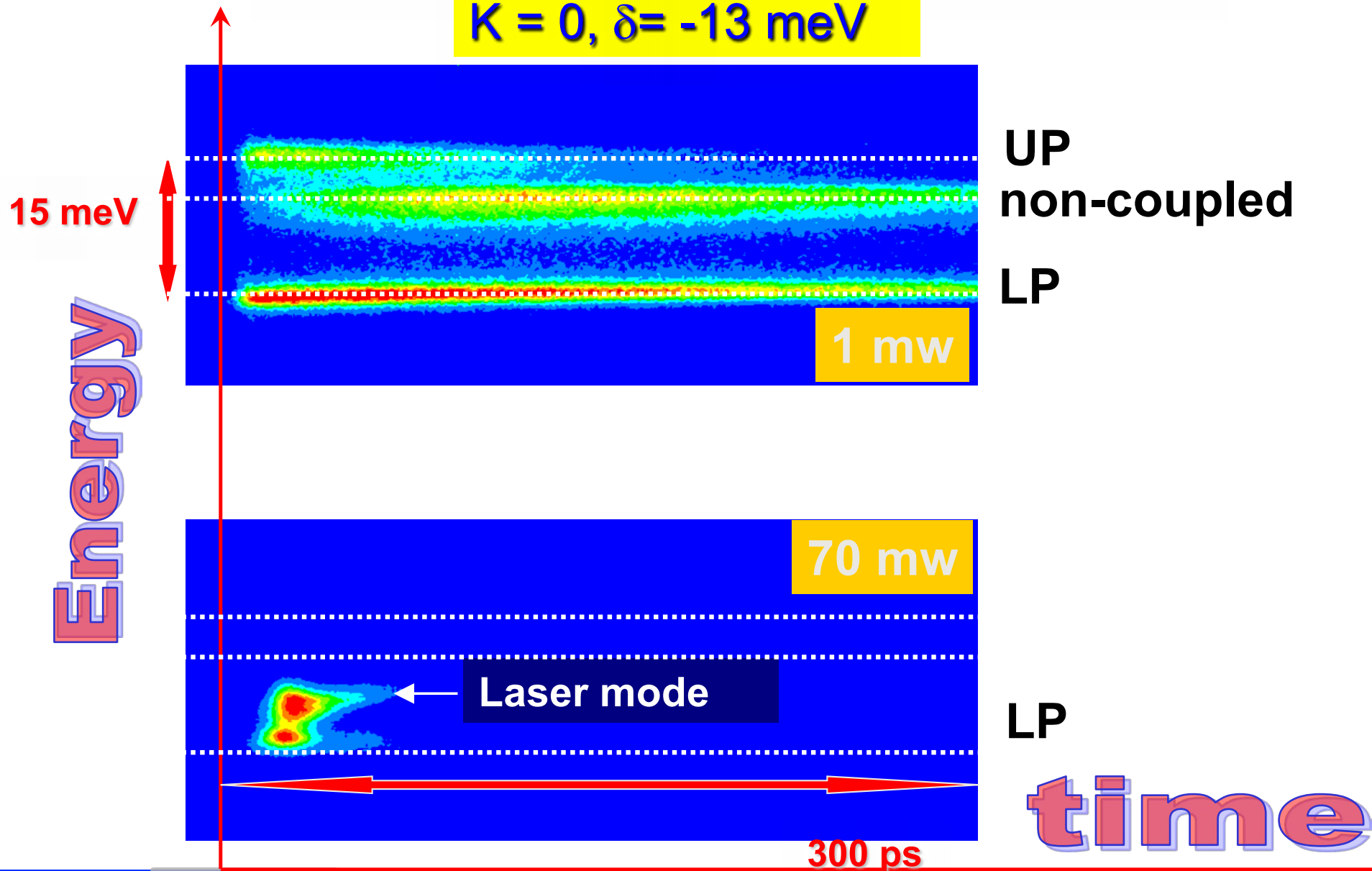


$K \approx 0$

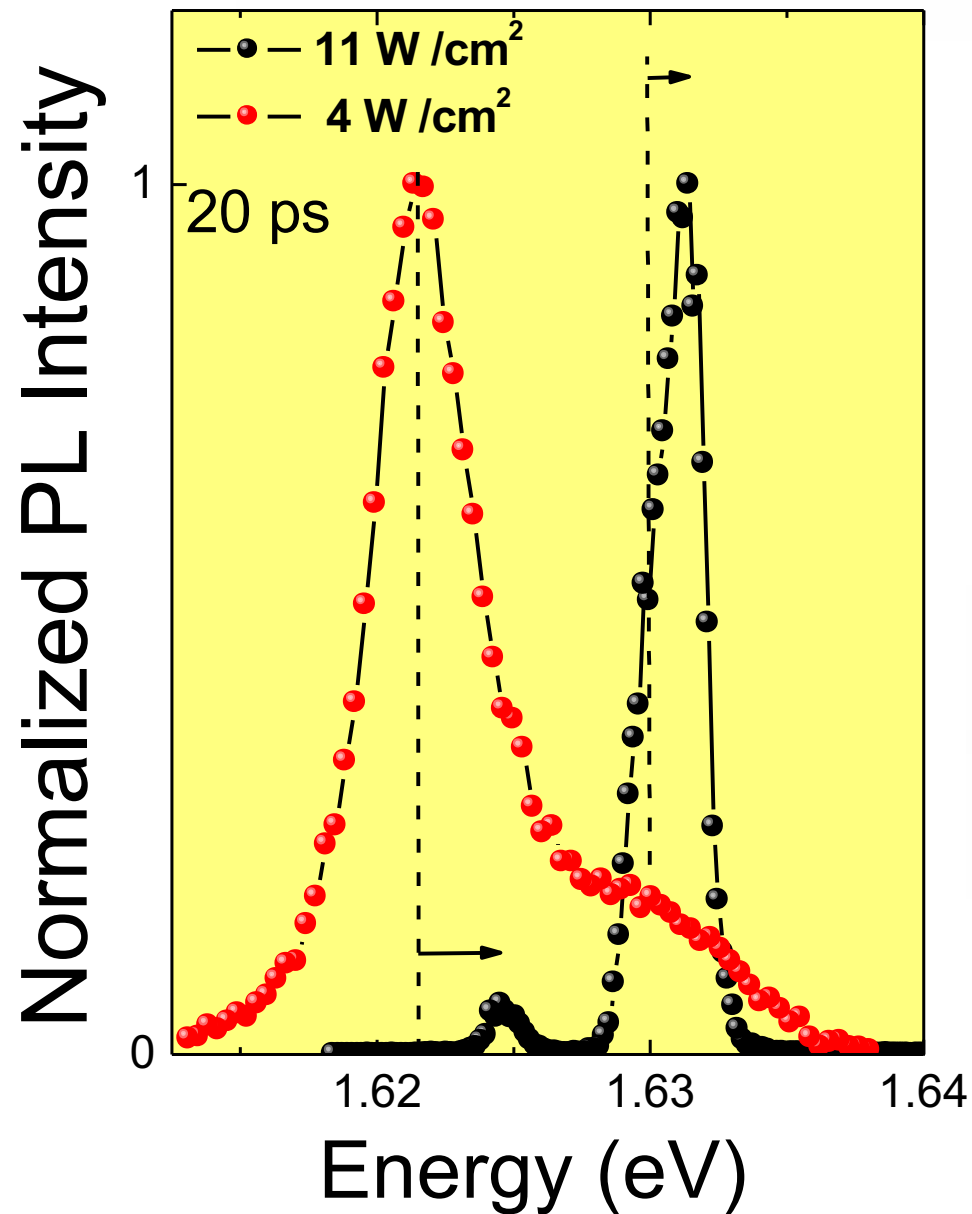


Non-linear regime (detail)

$K = 0, \delta = -13 \text{ meV}$



Non-linear regime (spectra)

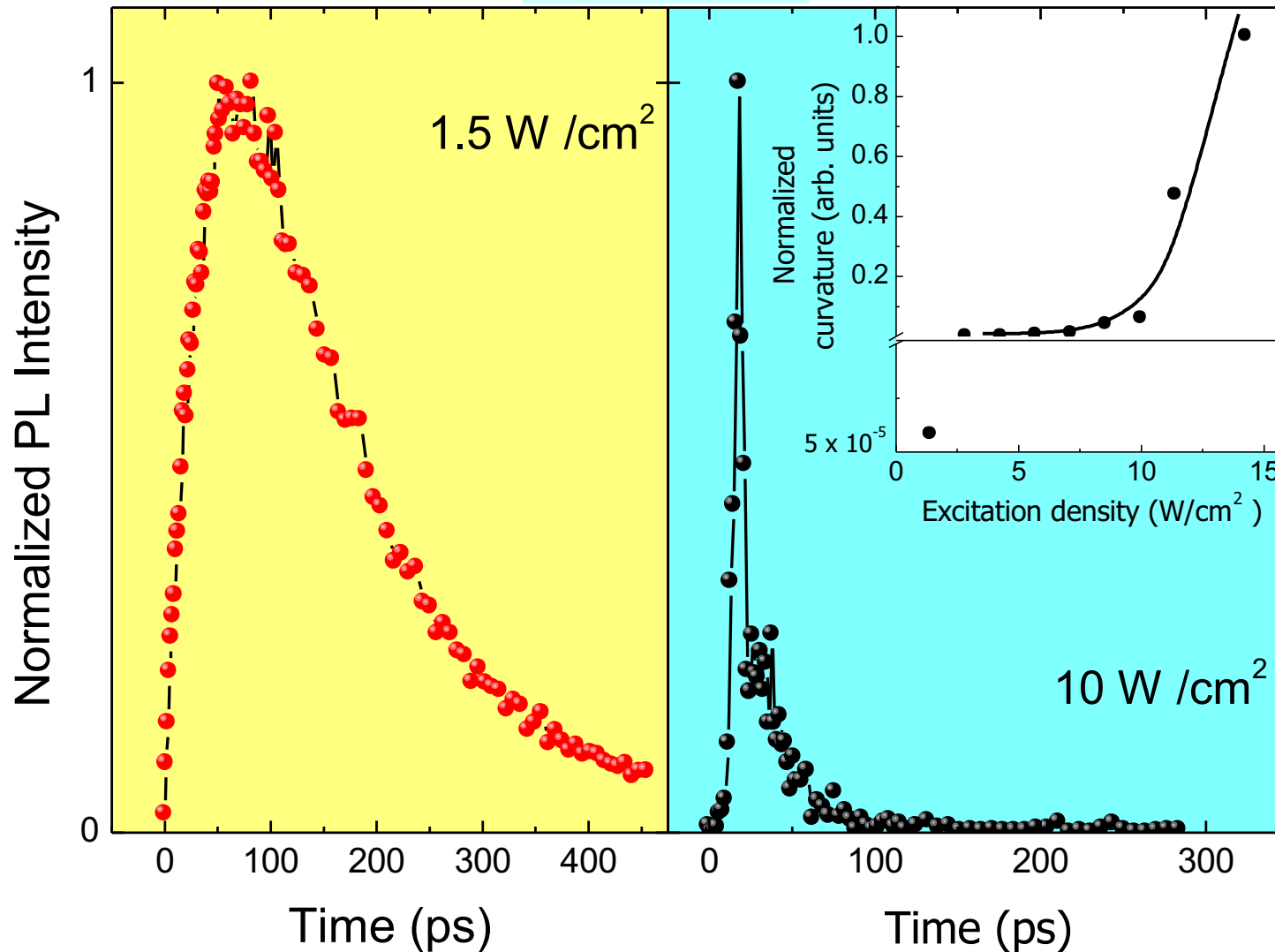


4 K

- ➡ Blue shift
- ➡ Line narrowing

Non-linear regime (dynamics 1)

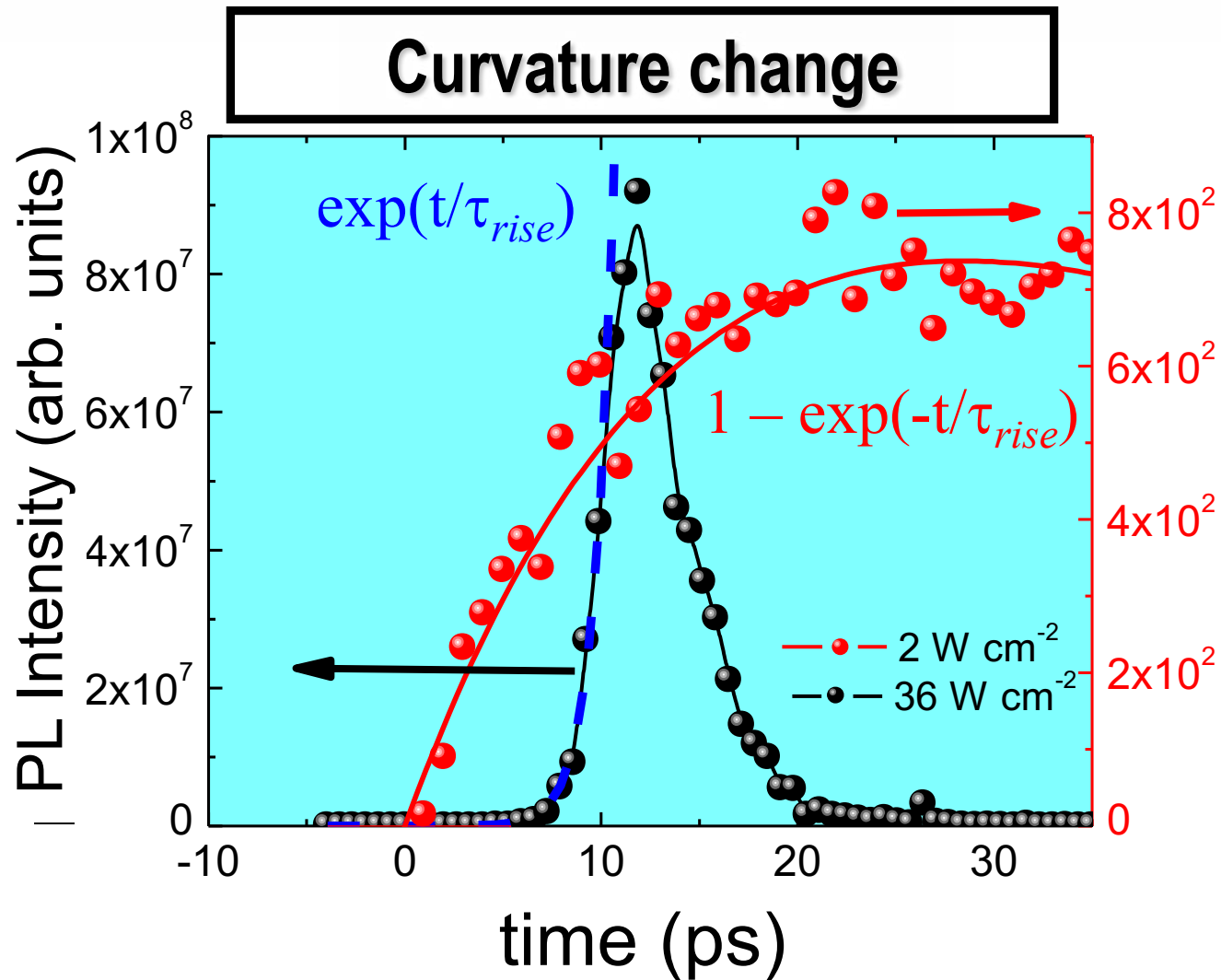
4 K



Initial
curvature
change

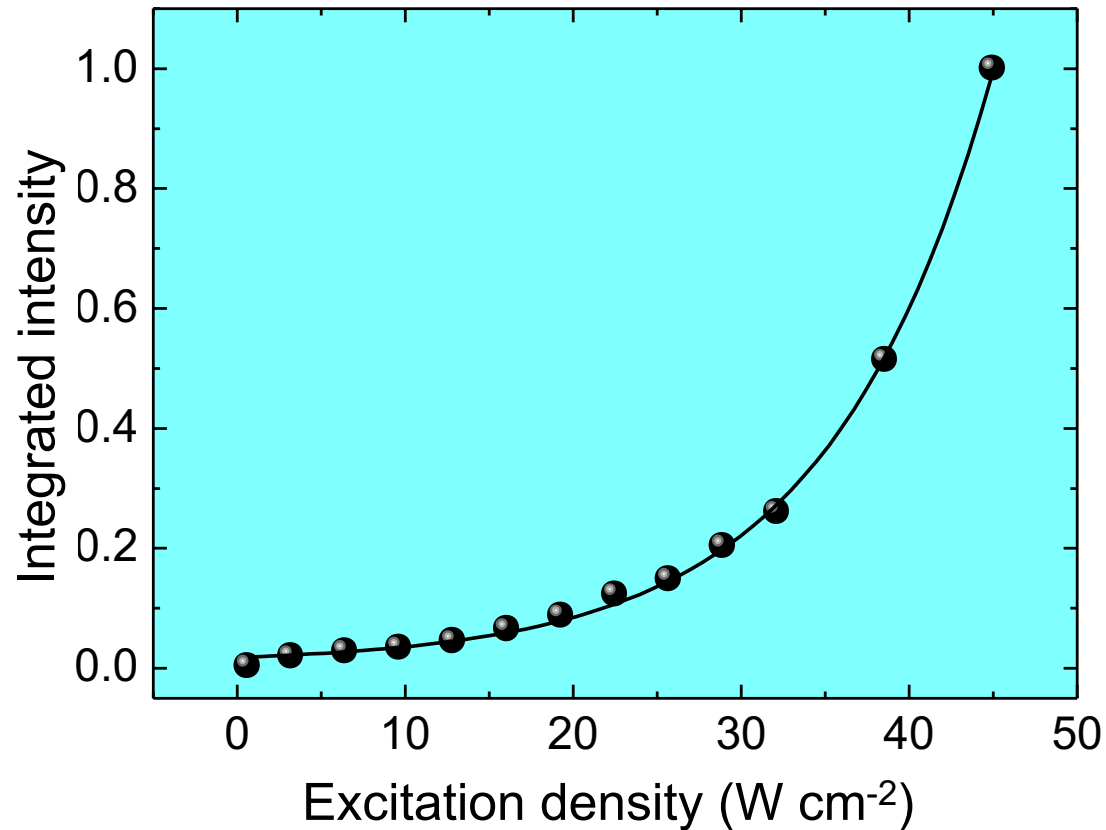
acceleration

Non-linear regime (dynamics 2)



Stimulated Scattering, exponential increase

Non-linear regime (intensities)



Stimulated Scattering

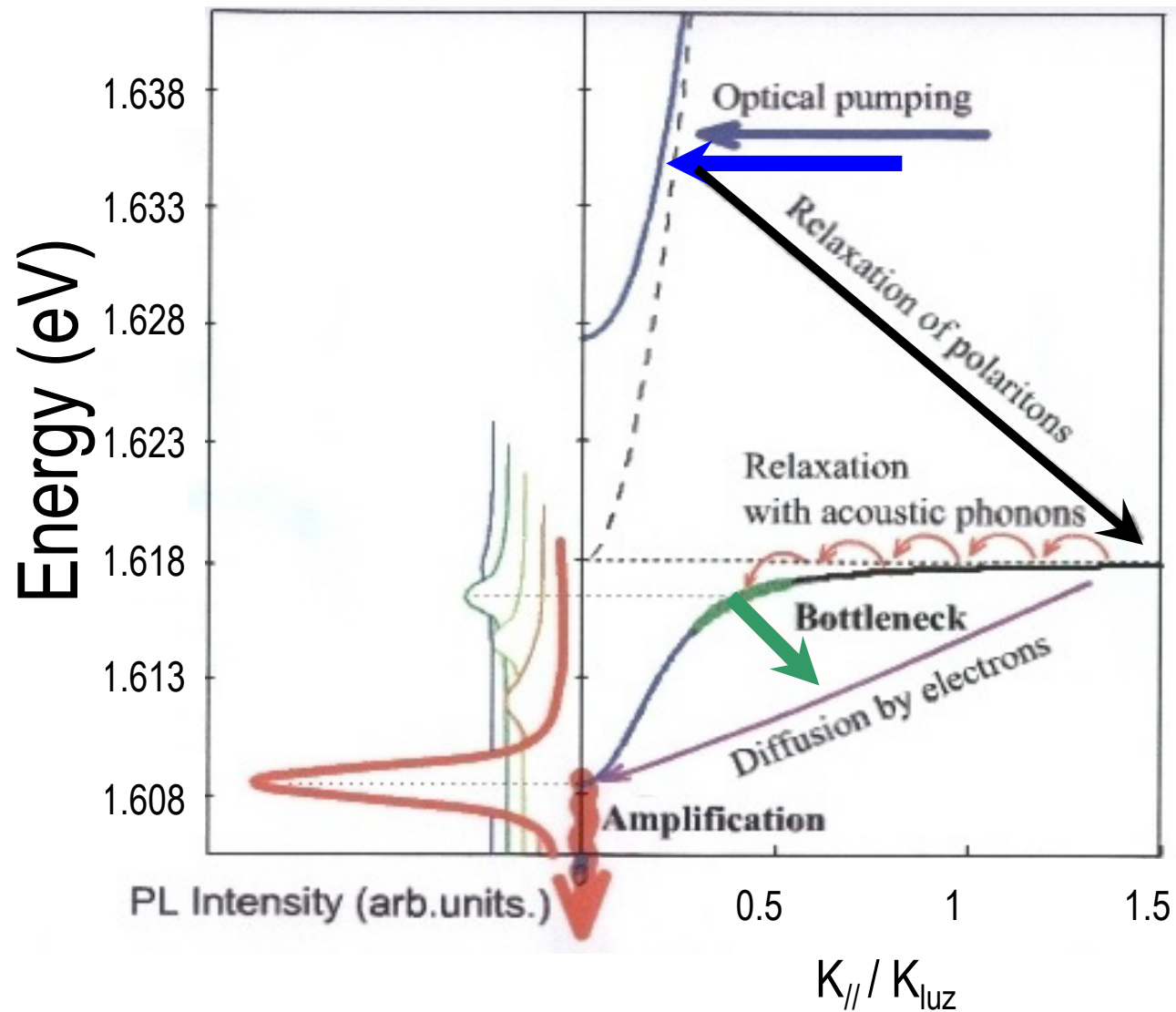
$$N_{final} \propto (1 + N_0) e^{I_{pump}}$$

Characteristics of non-linear regime

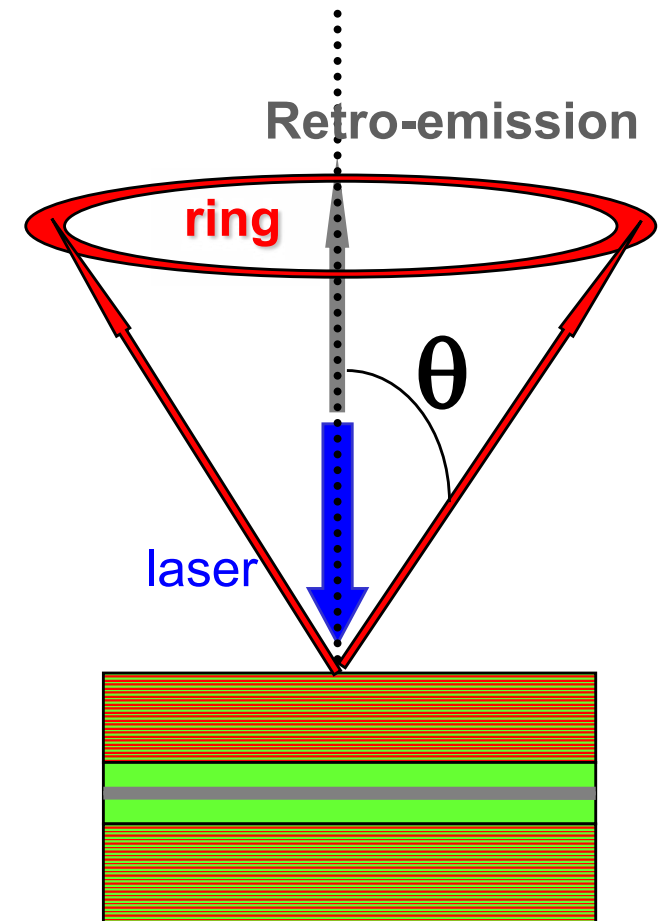
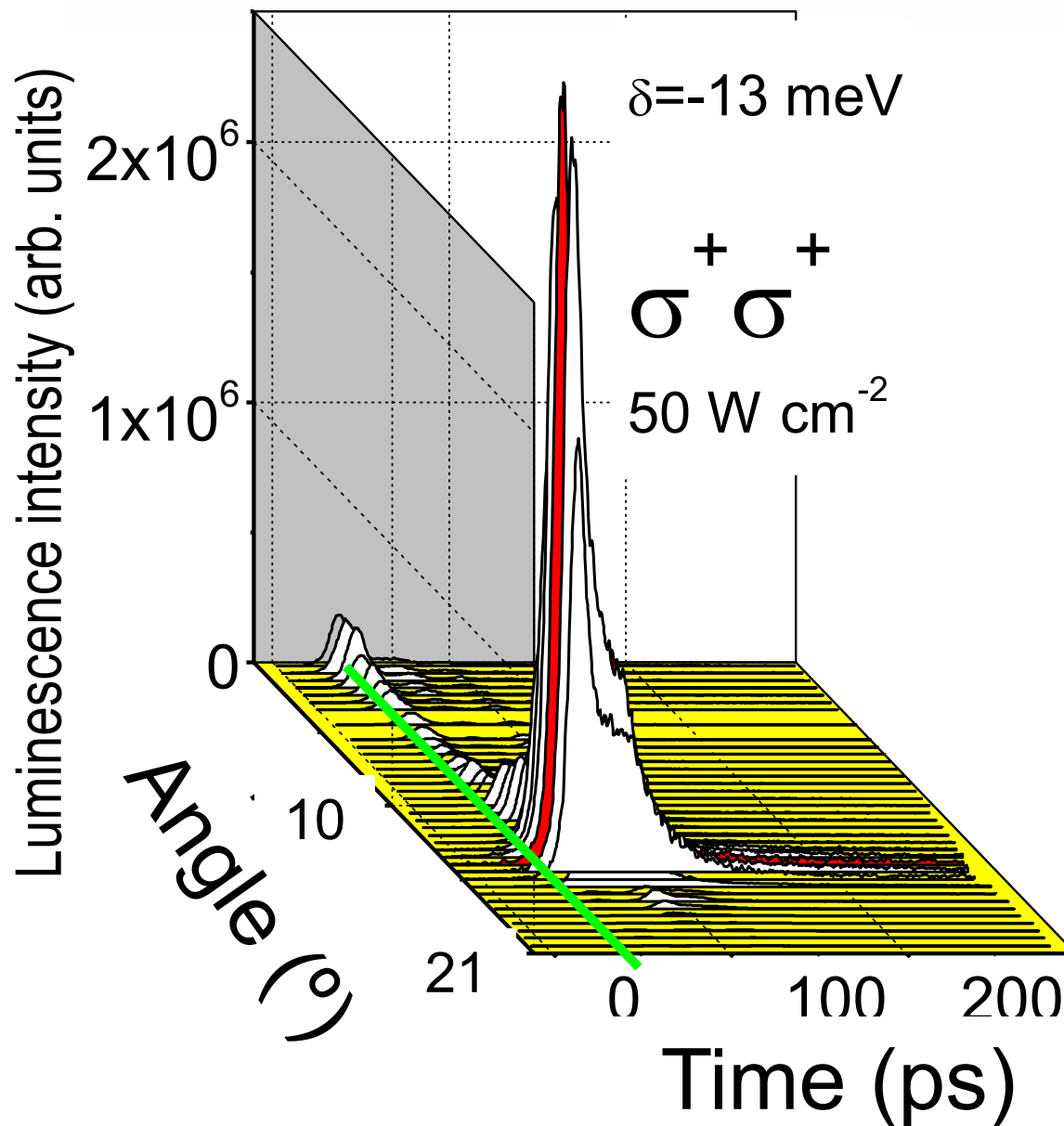
- ⇒ **Narrowing and shift of emission**
- ⇒ **Acceleration of the dynamics**
- ⇒ **Change in initial curvature**
- ⇒ **Exponential growth**

$K > 0$

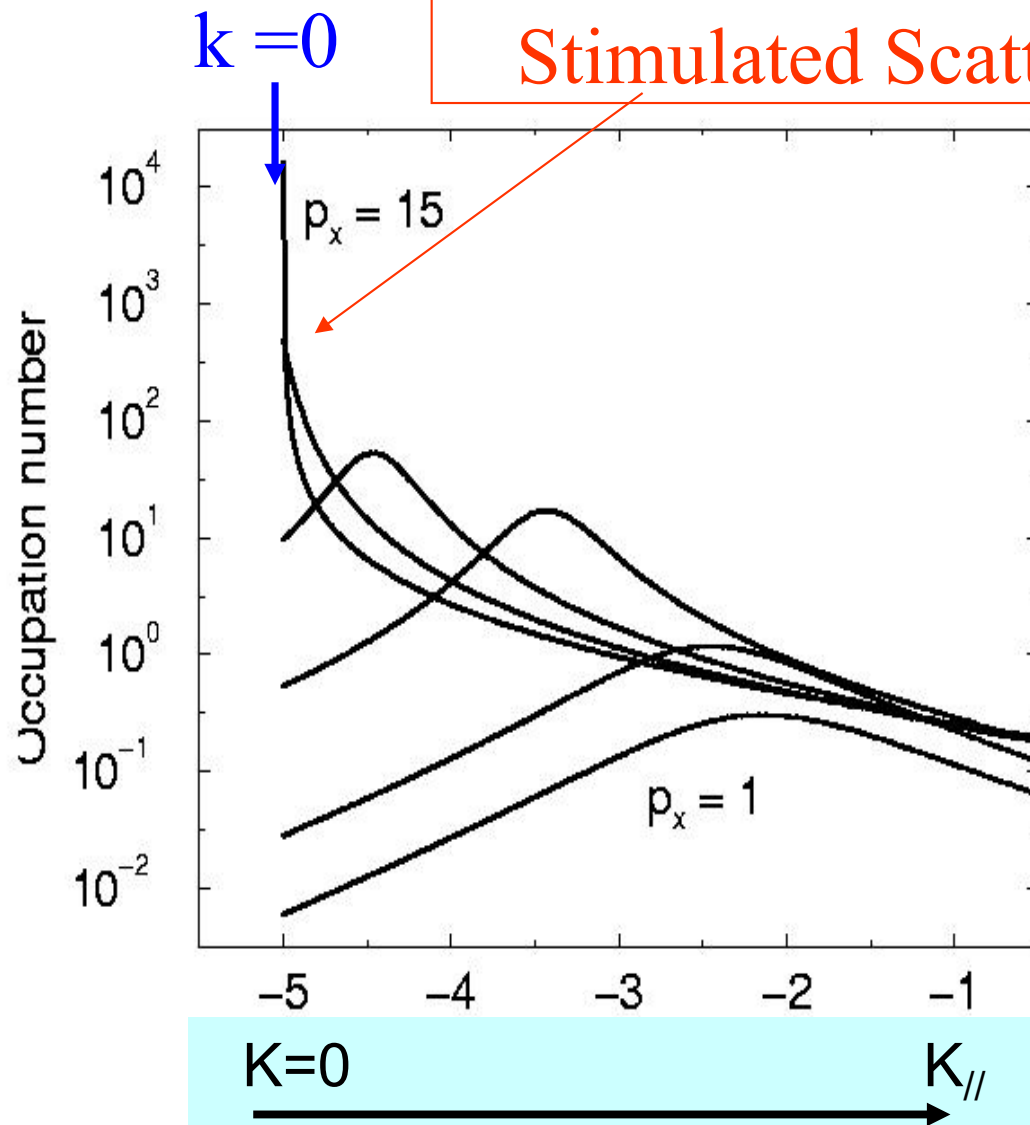
Relaxation along dispersion relation



Angular dependence of emission



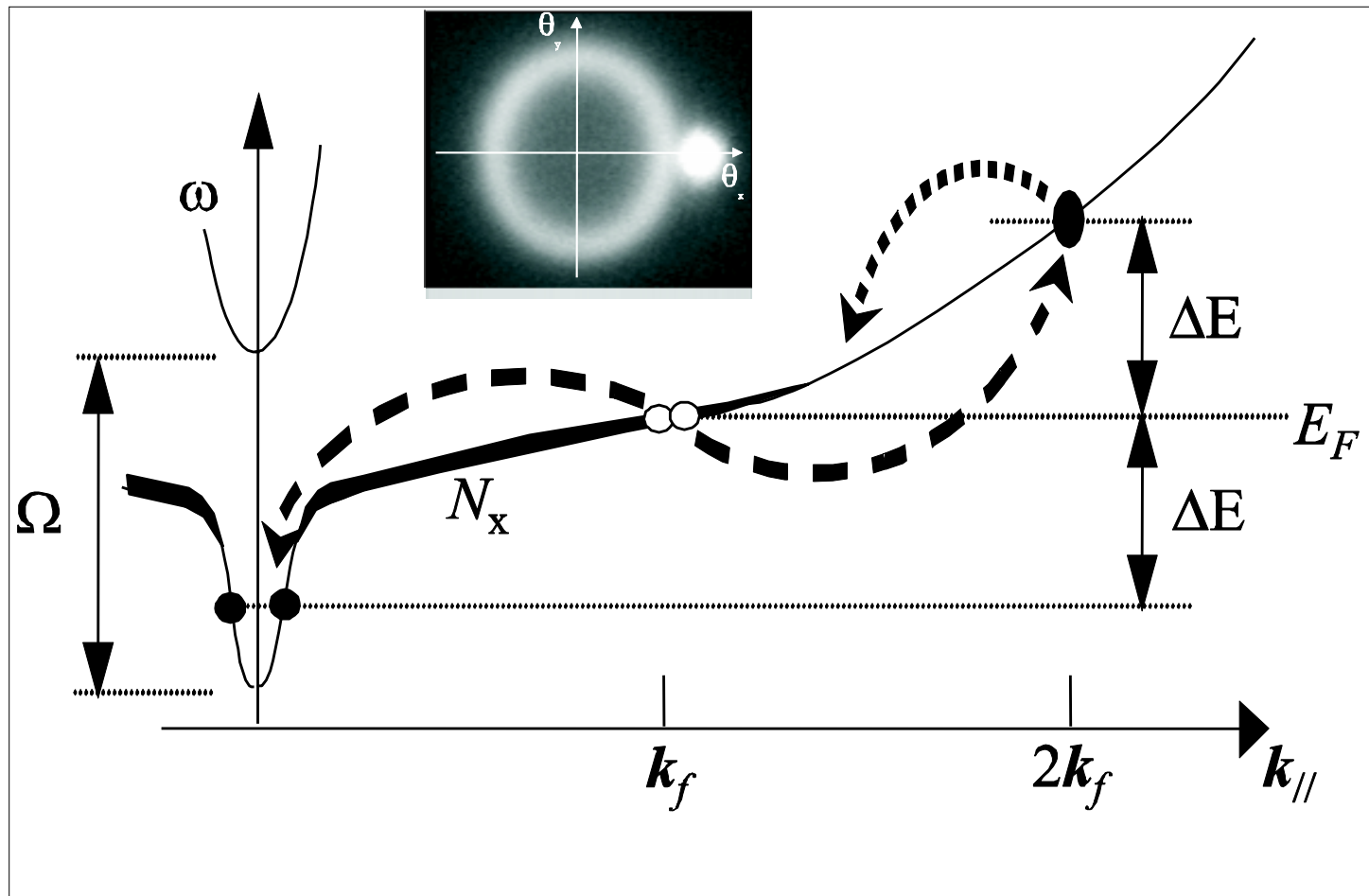
Occupation along dispersion



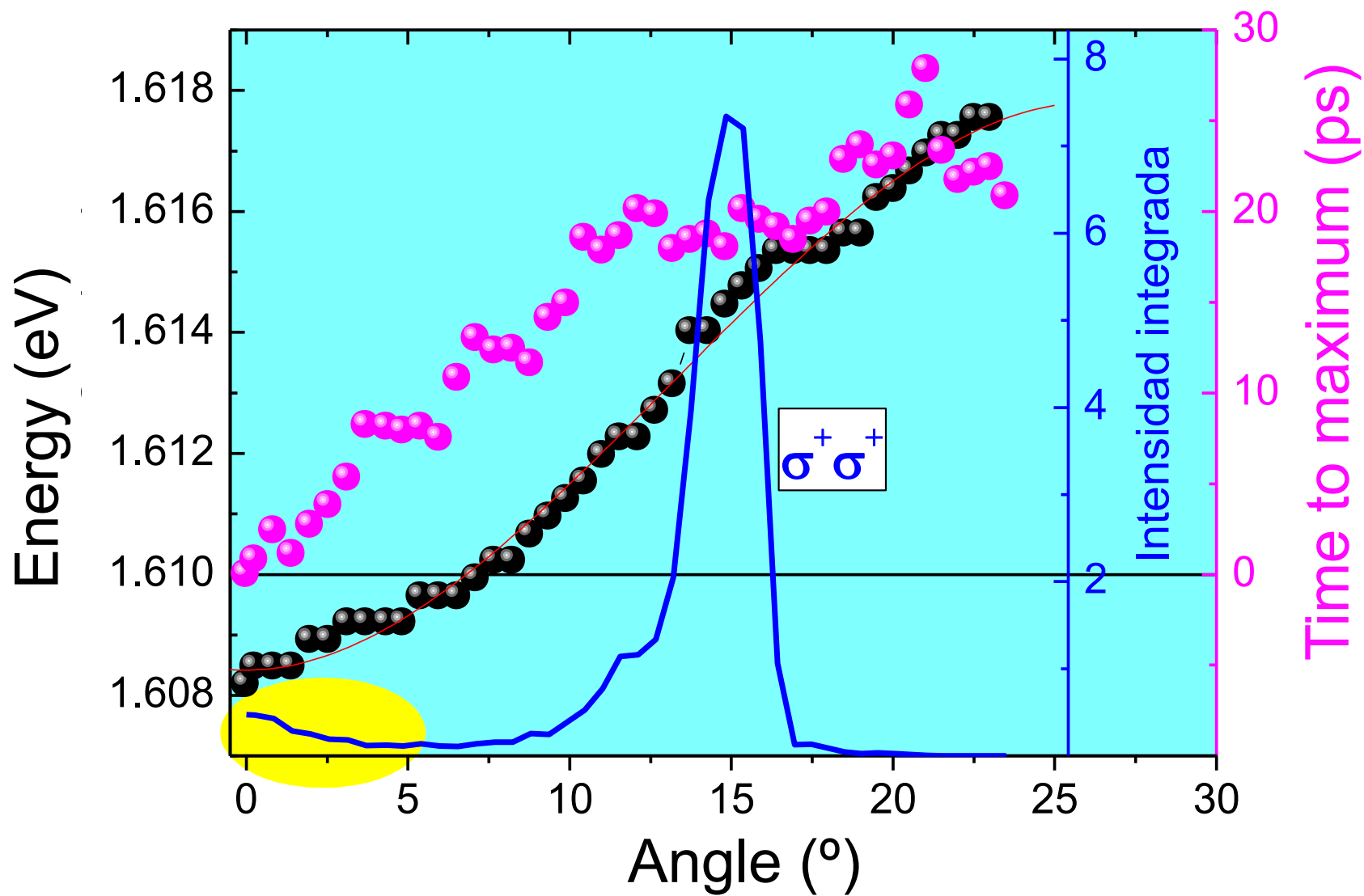
$$\delta = 0 ; \Omega_p = 10 \text{ meV}$$
$$T_L = 10 \text{ K}$$
$$p_x = 1, 2, 5, 8, 15 \cdot 10^8 \text{ cm}^{-2}/\text{ps}$$

D. Porras, C. Ciuti,
J. J. Baumberg, and C. Tejedor
Phys. Rev. B **66**, 085304 (2002)

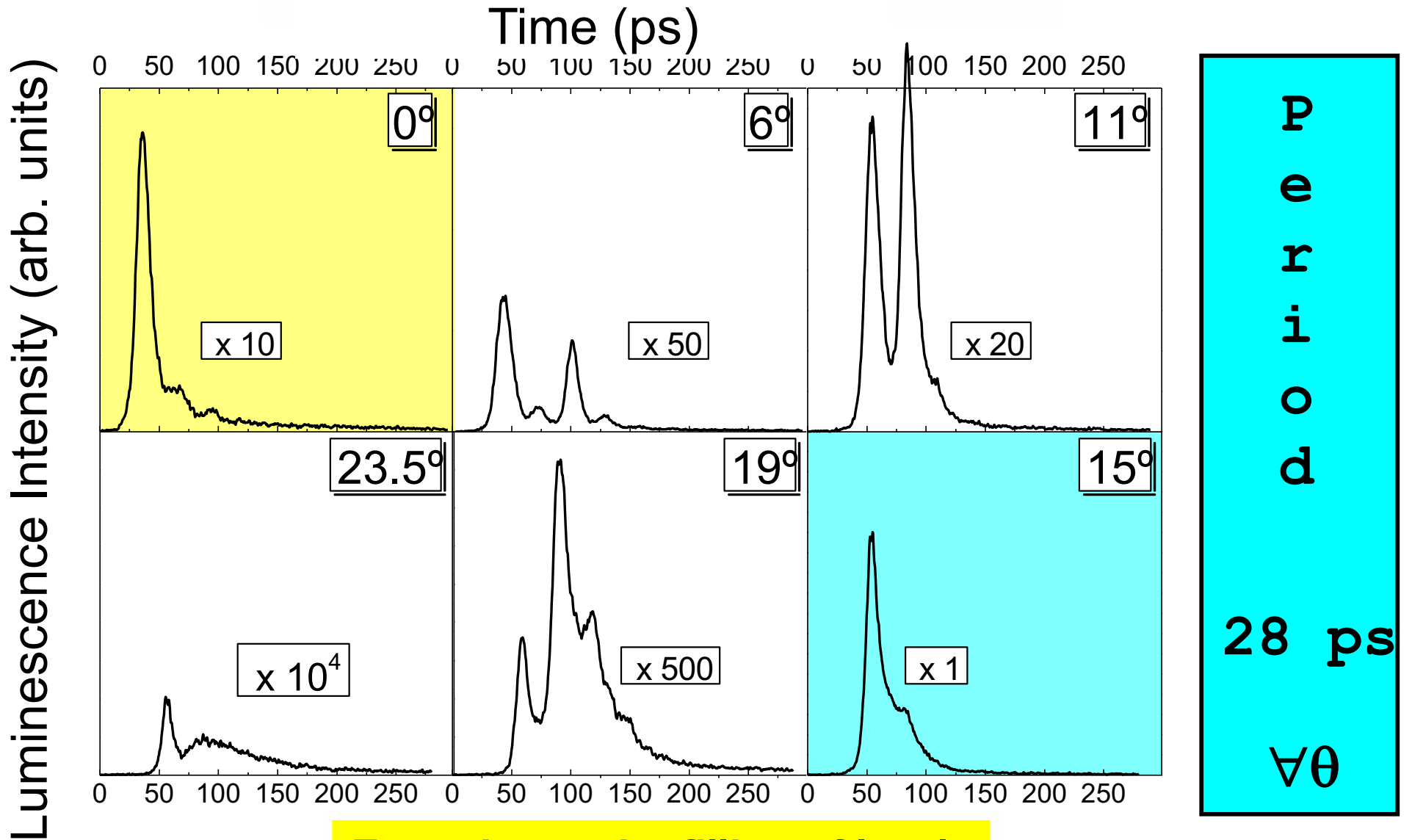
Ring formation



Ring formation dynamics



Oscillatory behavior

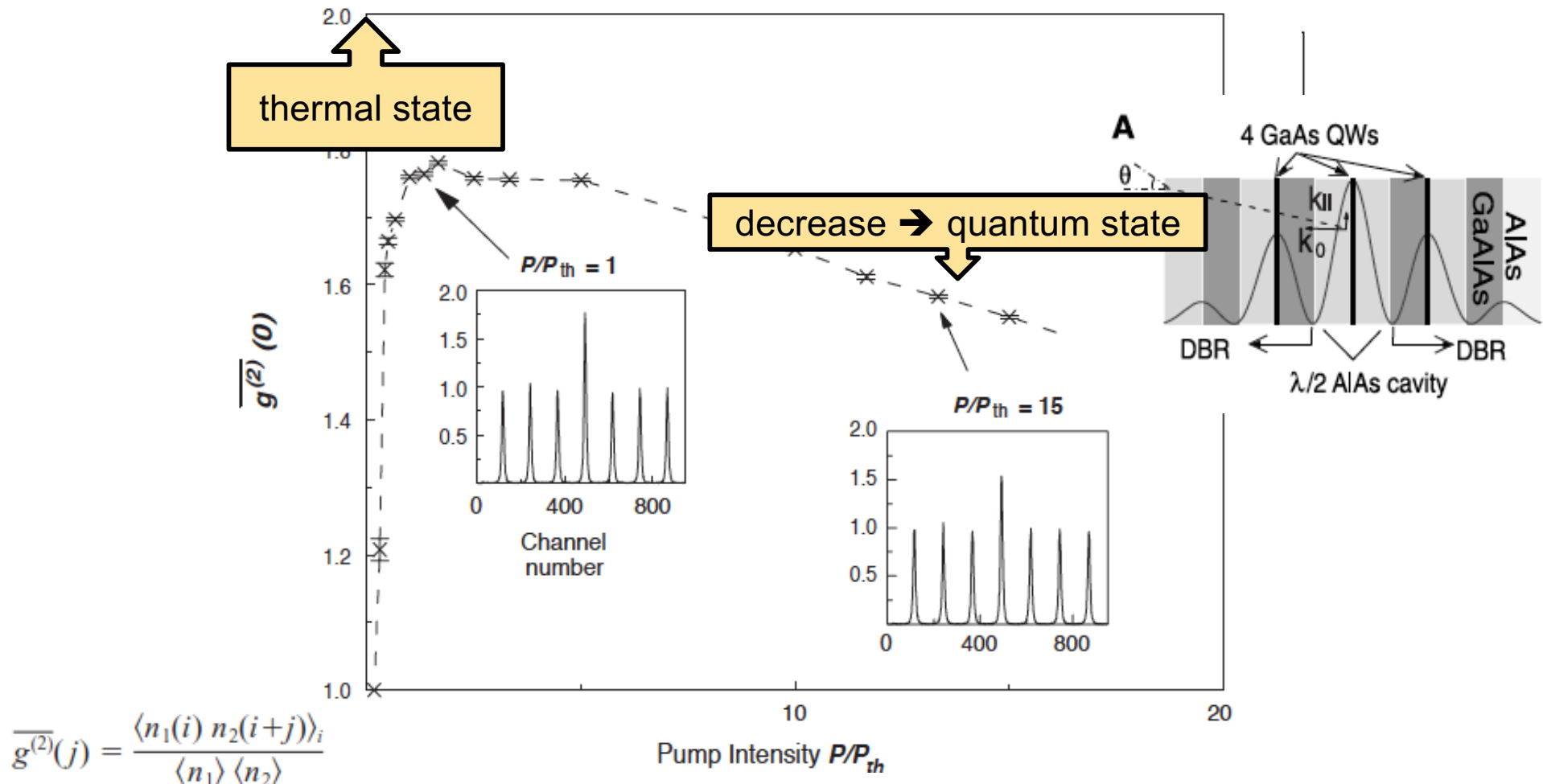


Emptying and refilling of levels

Some key studies

1st claim of “Condensation of Semiconductor μ -cavity Exciton Polaritons”

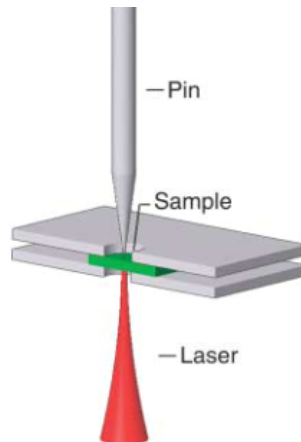
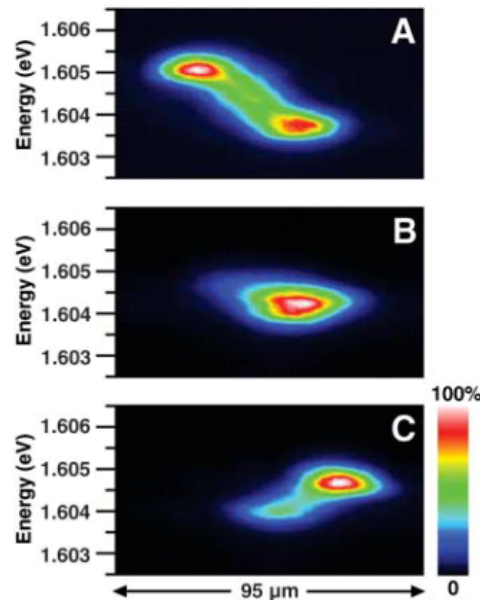
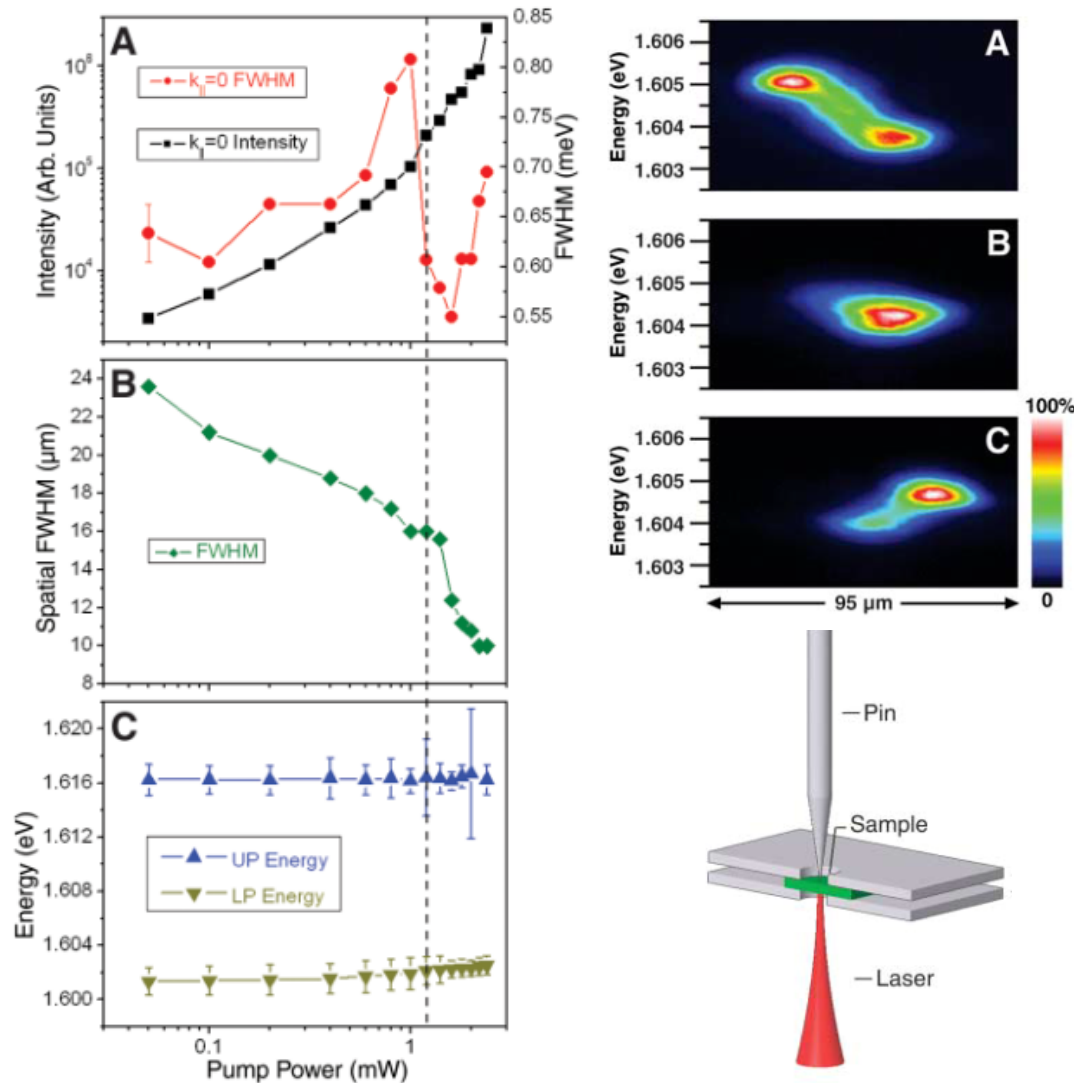
H. Deng, *et al.* Science **298**, 199 (2002)



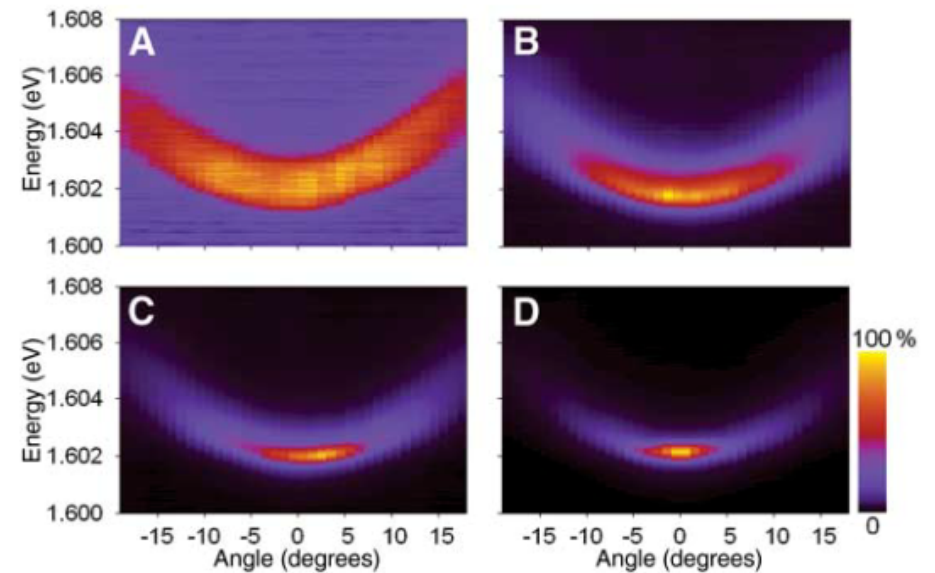
Some key studies

Polariton BEC in a trap

R. Balili, *et al.* Science 316, 1007 (2007)



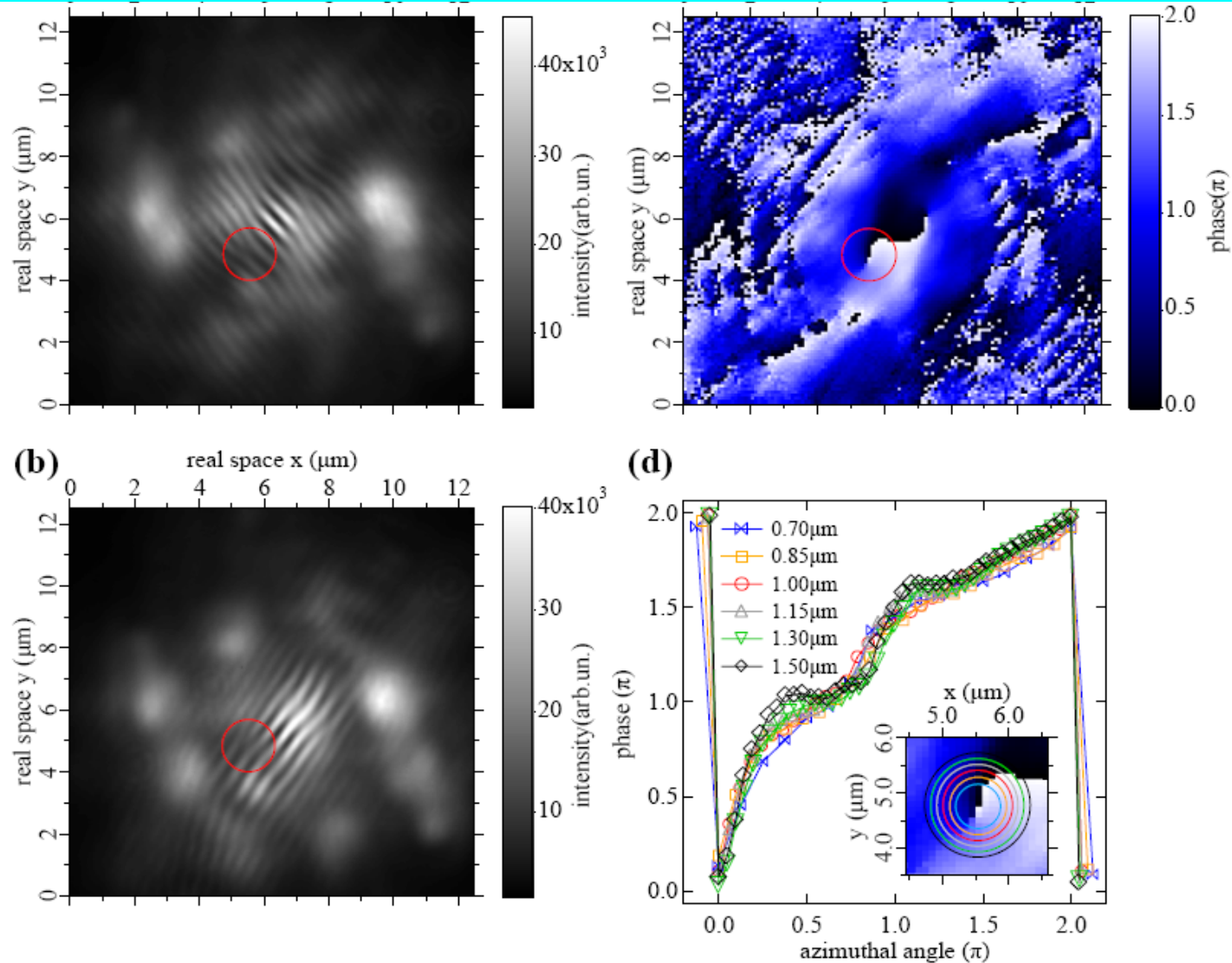
Increasing power density



Some key studies

Quantized Vortices in an Exciton-Polariton Fluid

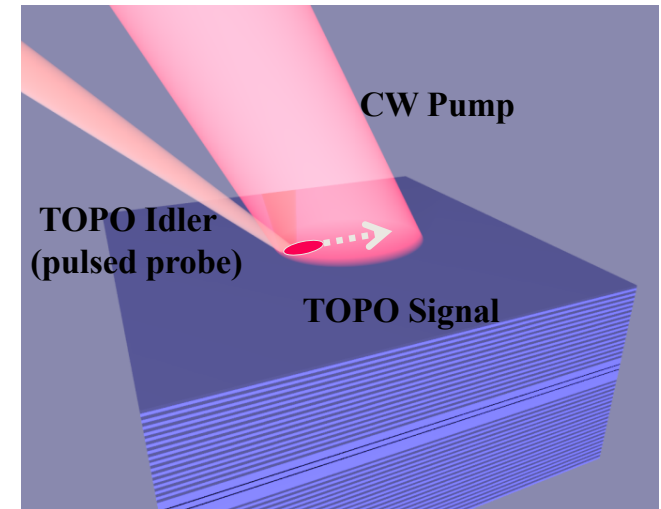
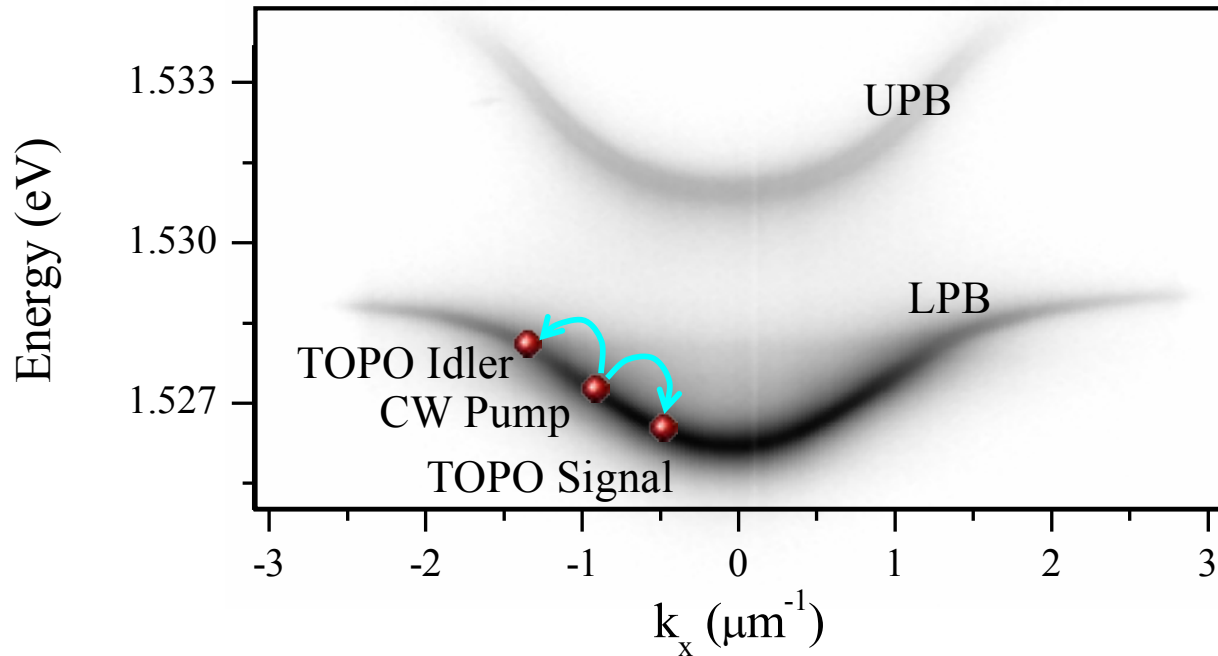
K.G. Lagoudakis, *et al.* Nature Physics 4, 706 (2008)



Some key studies

Coherent flow of polariton condensates

A.Amo, *et al.* Nature **457**, 291 (2009)



Coexistence of **two fluids** with different velocities:

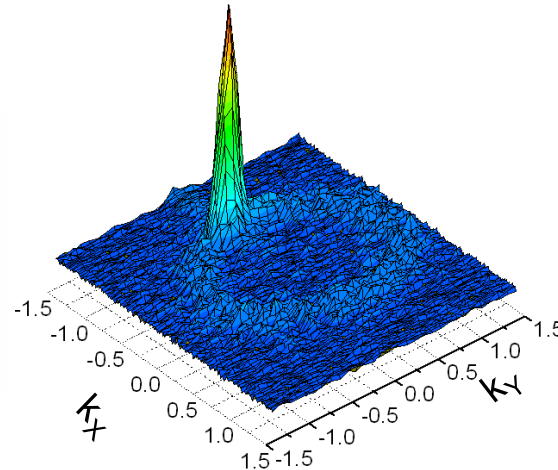
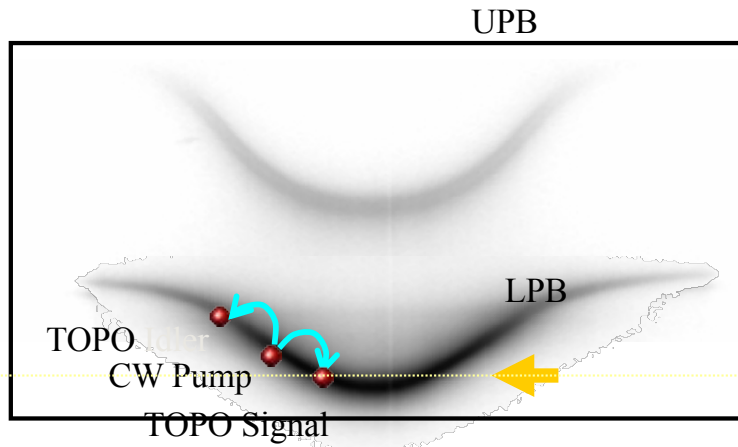
$$v_g = \frac{1}{\hbar} \frac{\partial E}{\partial k} > 0 \quad \rightarrow$$

- Steady state CW (pump) ← large spot
- Triggered OPO (signal) ← small initial spot

Some key studies

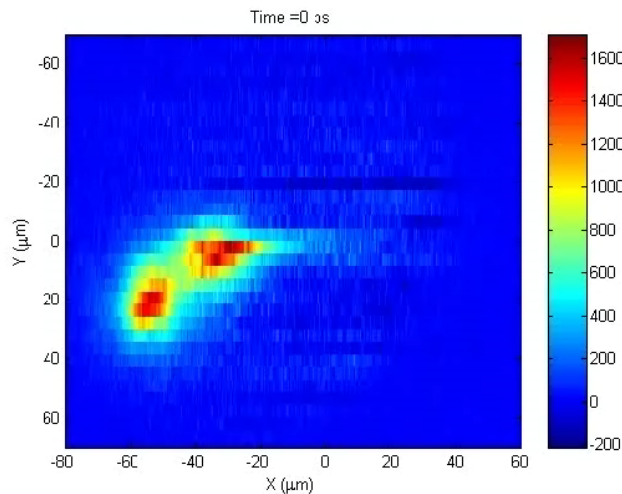
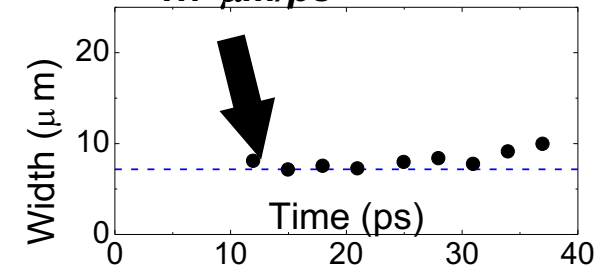
Coherent flow of polariton condensates

A.Amo, *et al.* Nature 457 , 291 (2009)

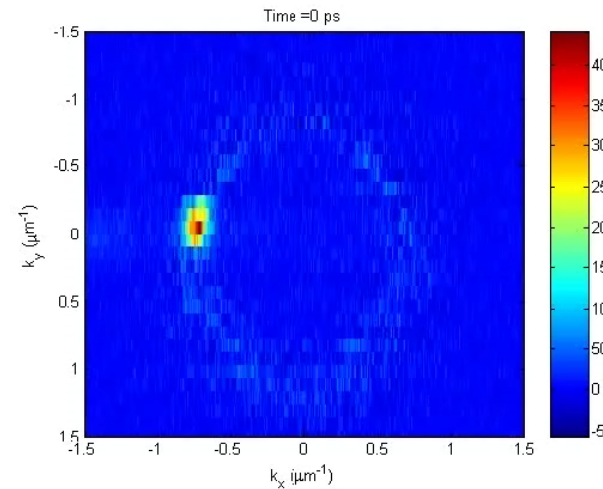


High pump power (blueshift)

- Unperturbed flow: no expansion
 - Well defined k
 - $1.7 \mu\text{m/ps}$



real space

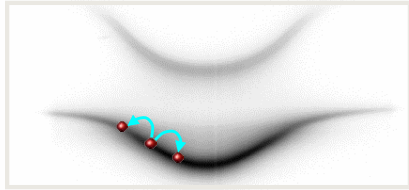


momentum space

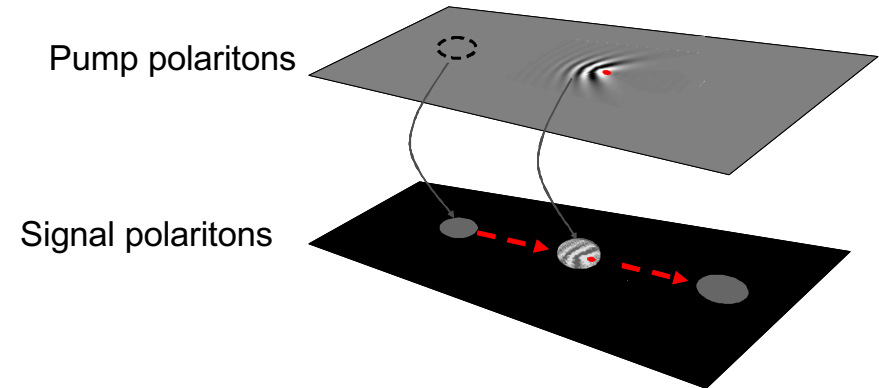
Some key studies

Coherent flow of polariton condensates

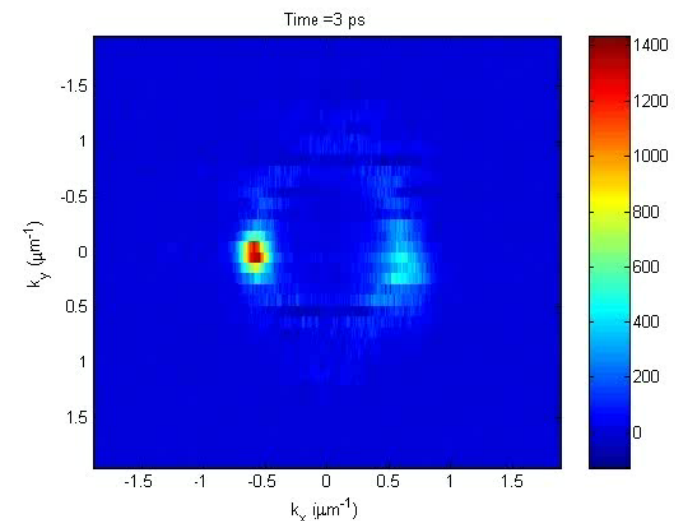
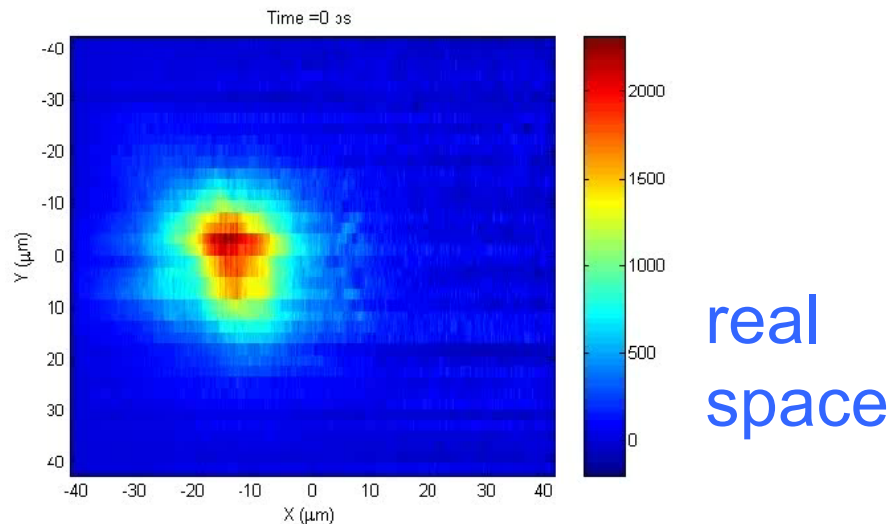
A.Amo, *et al.* Nature **457**, 291 (2009)



- The defect is observed through the Čerenkov waves present at the pump state
- Signal fluid
no scattering with the defect
well defined momentum

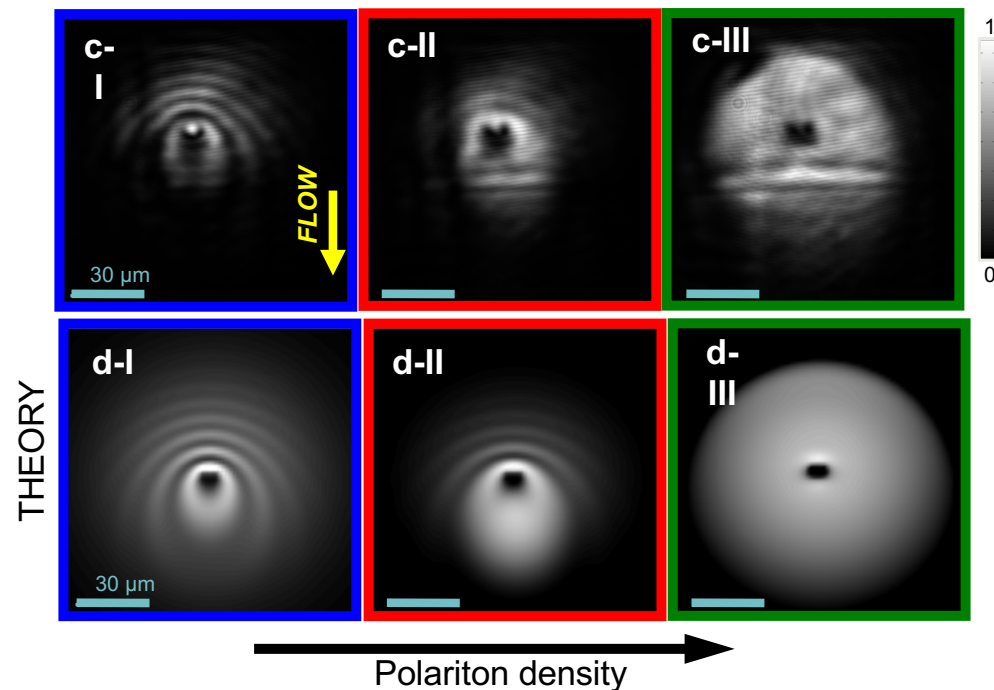


momentum space



Some key studies

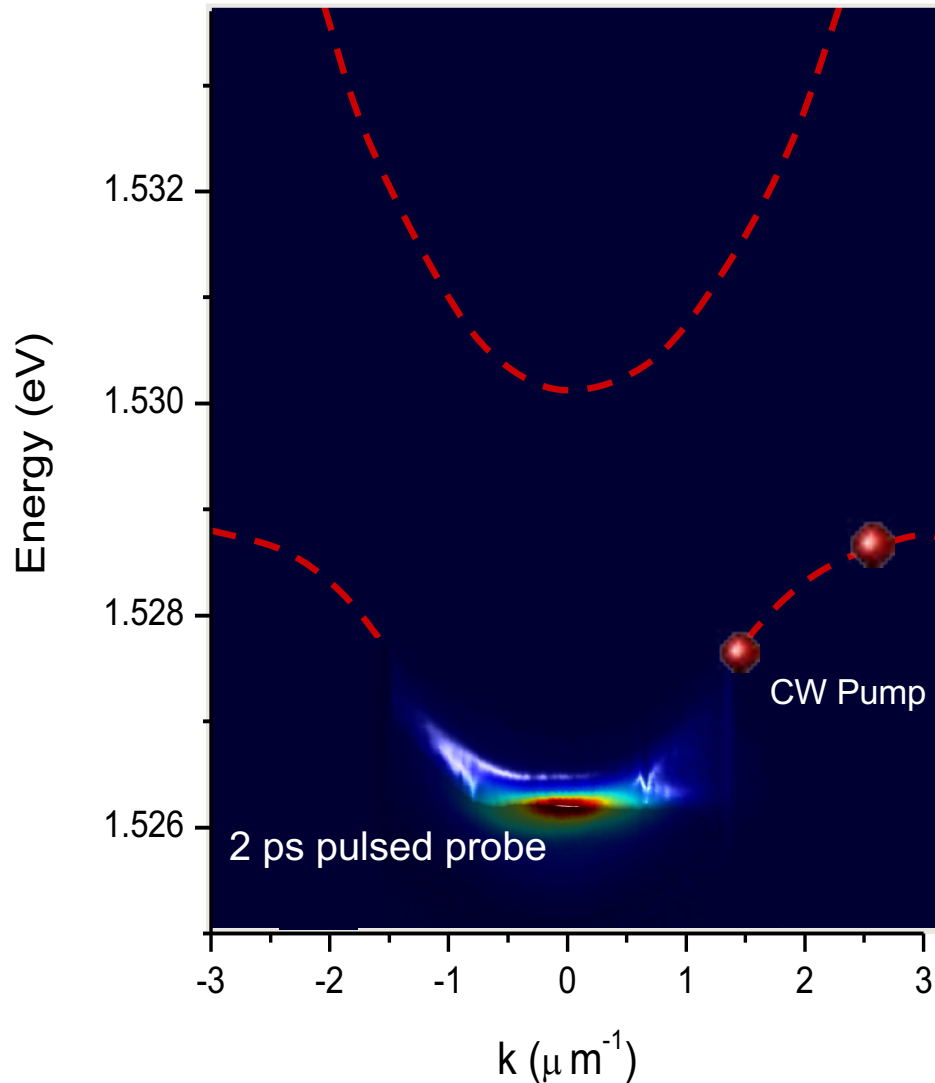
Superfluidity of polaritons in semiconductor microcavities
A. Amo, *et al.*, Nature Physics 5, 805 (2009)



Observation a pump polariton state at
velocities above and below the speed of sound

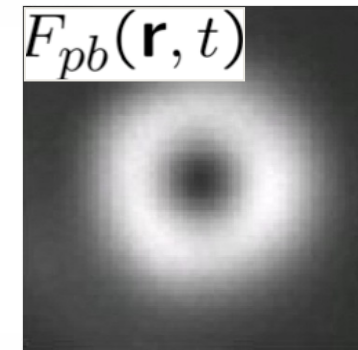
Some key studies

Vortex Dynamics in an Exciton-Polariton Fluid
D. Sanvitto, *et al.*, Nature Physics 6, 527 (2010)

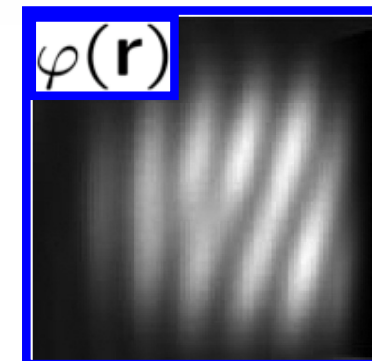


$$F_{pb}(\mathbf{r}, t) = \mathcal{F}_{pb}(\mathbf{r}) e^{i\varphi(\mathbf{r})} e^{-\frac{t^2}{2\sigma_t^2}} e^{i(\mathbf{k}_s \cdot \mathbf{r} - \omega_{st})}$$

Vortex state of light



Typical interferences
with a mirrored image

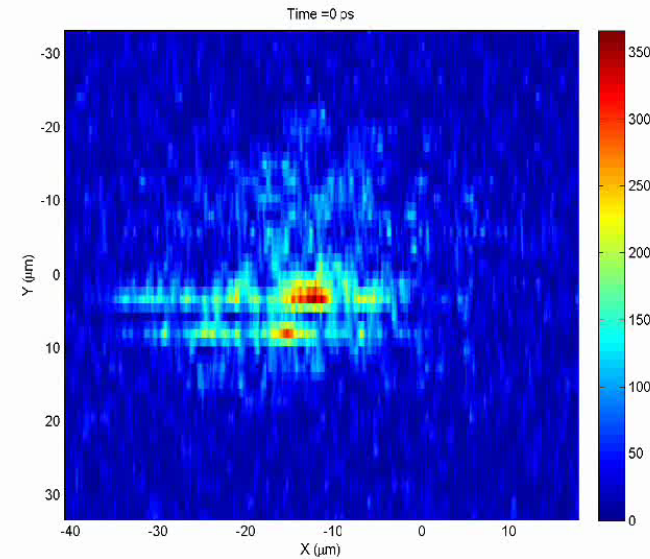
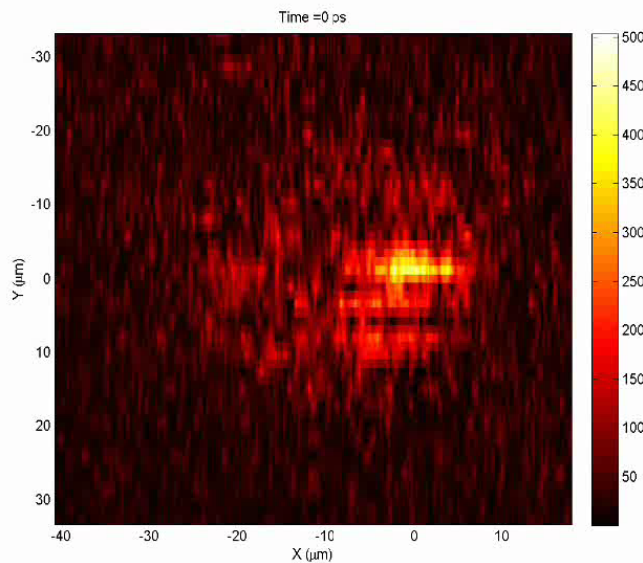


Some key studies

Vortex Dynamics in an Exciton-Polariton Fluid
D. Sanvitto, *et al.*, Nature Physics 6, 527 (2010)

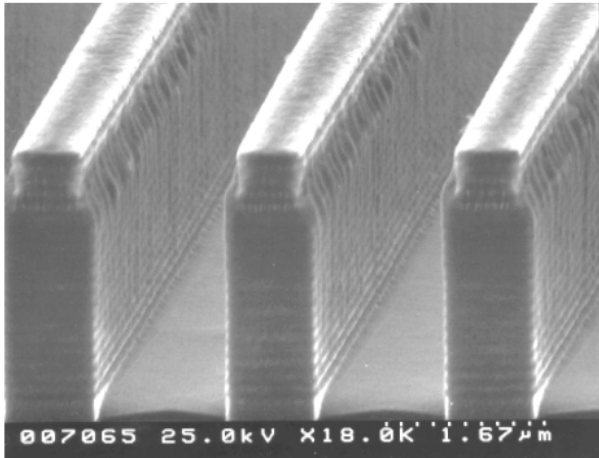
2D Movies of the experiment injecting
a $m=1$ vorticity

Real space image of the signal emission Interference pattern of the signal

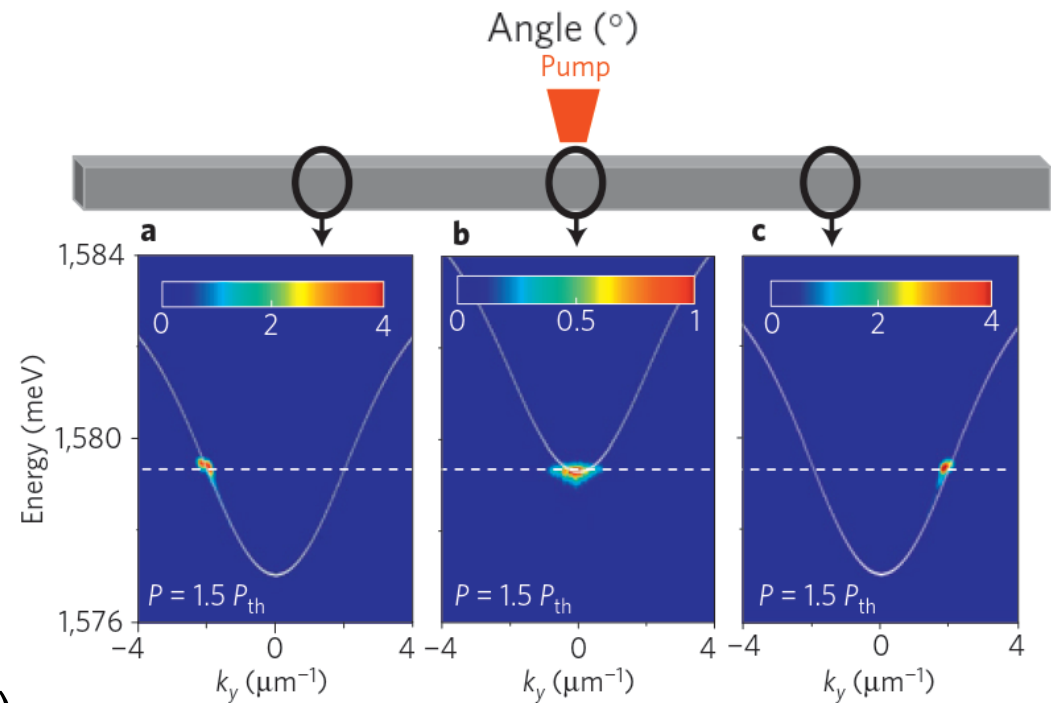
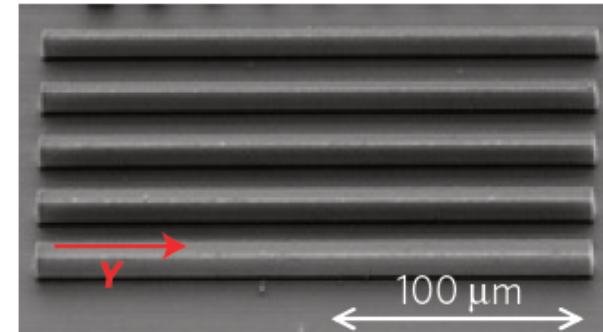


Some key studies

Patterning of μ -cavities



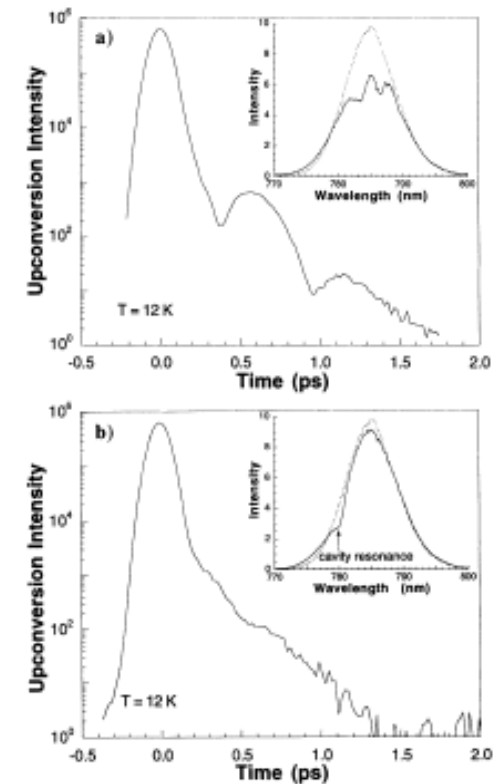
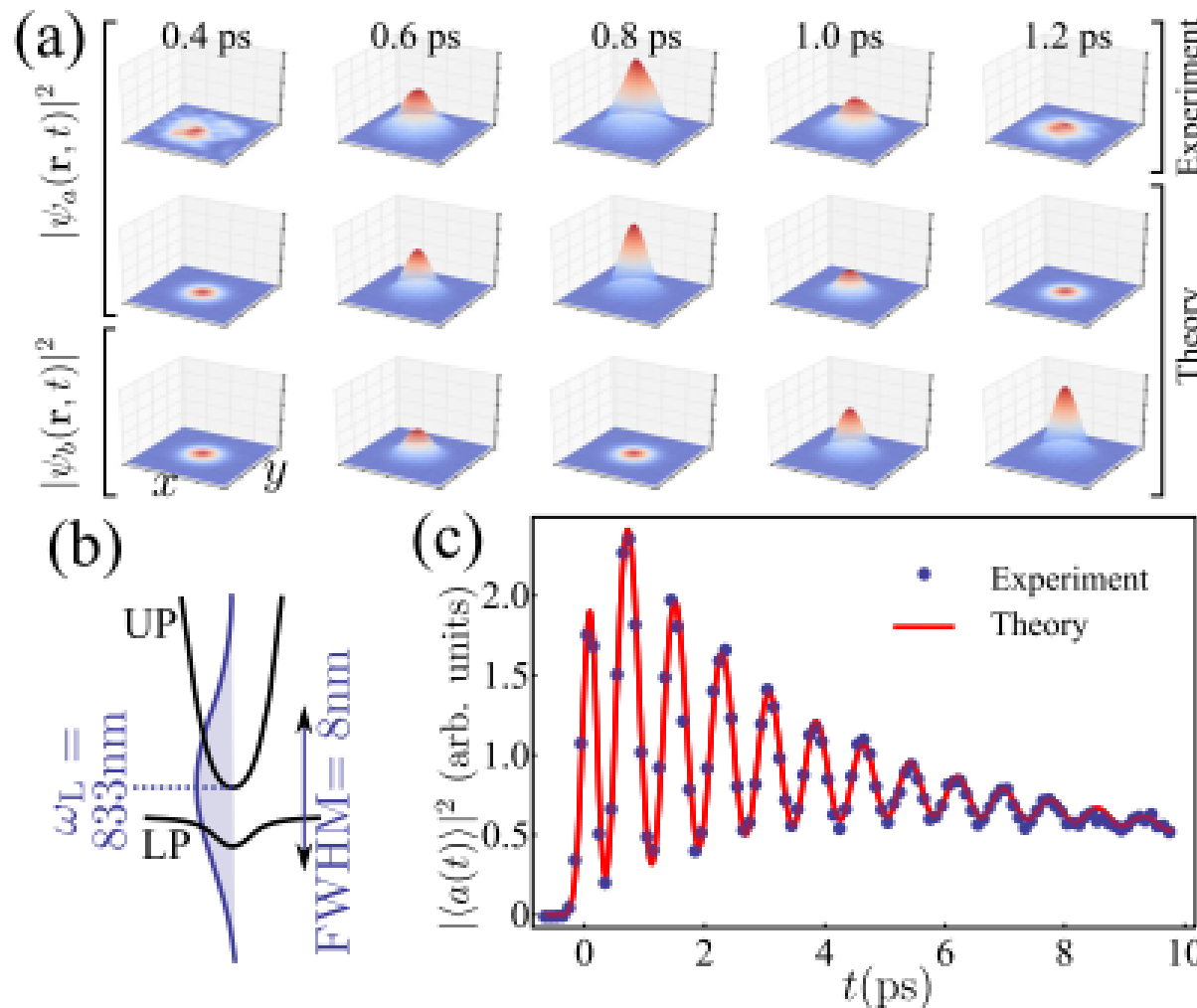
A. Kuther, *et al.*,
Phys. Rev. B **58**, 15744 (1998)



E. Wertz, *et al.*,
Nature Physics **6**, 860 (2010)

Some key studies

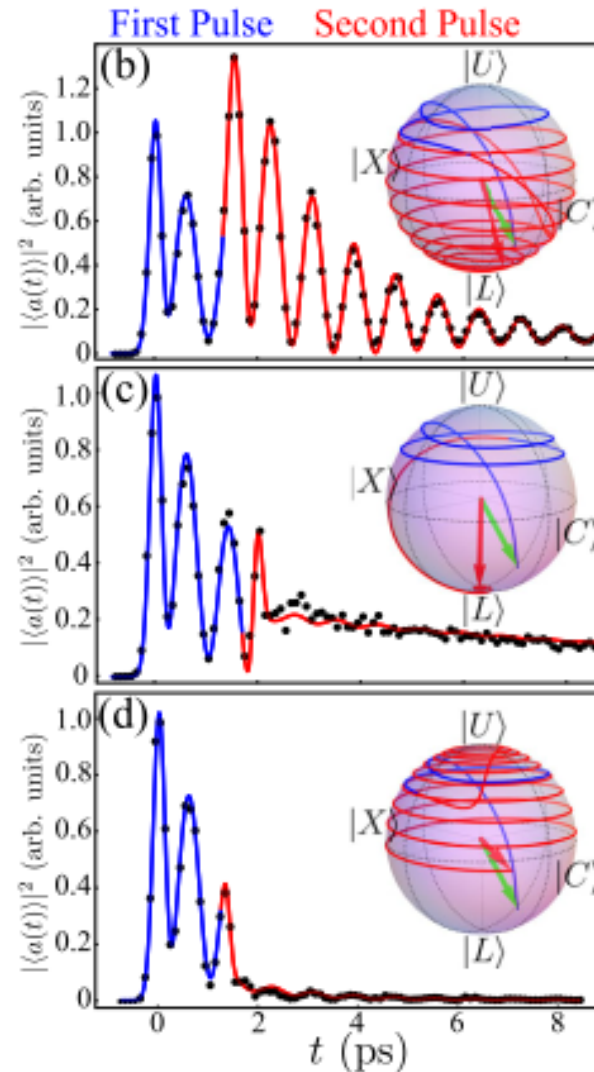
Ultrafast Control and Rabi Oscillations of Polaritons
 L. Dominici, et al., Phys. Rev. Lett. **113**, 226401 (2014)



64

Some key studies

Ultrafast Control and Rabi Oscillations of Polaritons
L. Dominici, et al., Phys. Rev. Lett. **113**, 226401 (2014)



Amplification

From p \rightarrow LP

Annihilation

65

More to come